

16M-BIT [x 1 / x 2] CMOS SERIAL FLASH 32M-BIT [x 1 / x 2] CMOS SERIAL FLASH 64M-BIT [x 1 / x 2] CMOS SERIAL FLASH

FEATURES

GENERAL

- Serial Peripheral Interface compatible -- Mode 0 and Mode 3
- 16M:16,777,216 x 1 bit structure or 8,388,608 x 2 bits (two I/O read mode) structure 32M:33,554,432 x 1 bit structure or 16,772,216 x 2 bits (two I/O read mode) structure 64M:67,108,864 x 1 bit structure or 33,554,432 x 2 bits (two I/O read mode) structure
- 512 Equal Sectors with 4K byte each (16Mb)
 1024 Equal Sectors with 4K byte each (32Mb)
 - 2048 Equal Sectors with 4K byte each (64Mb)
- Any Sector can be erased individually
 32 Equal Blocks with 64K byte each (16Mb)
 - 64 Equal Blocks with 64K byte each (32Mb)
 - 128 Equal Blocks with 64K byte each (64Mb)
 - Any Block can be erased individually
- Single Power Supply Operation
 - 2.7 to 3.6 volt for read, erase, and program operations
- Latch-up protected to 100mA from -1V to Vcc +1V
- Low Vcc write inhibit is from 1.5V to 2.5V

PERFORMANCE

- · High Performance
 - Fast access time: 86MHz serial clock (15pF + 1TTL Load) and 66MHz serial clock (30pF + 1TTL Load)
 - Serial clock of two I/O read mode: 50MHz (15pF + TTL Load), which is equivalent to 100MHz
 - Fast program time: 1.4ms(typ.) and 5ms(max.)/page (256-byte per page)
 - Byte program time: 9us (typical)
 - Continuously program mode (automatically increase address under word program mode)
 - Fast erase time: 60ms(typ.) /sector (4K-byte per sector); 0.7s(typ.) /block (64K-byte per block); 14s(typ.) /chip for 16Mb, 25s(typ.) for 32Mb, and 50s(typ.) for 64Mb
- Low Power Consumption
 - Low active read current: 25mA(max.) at 86MHz, 20mA(max.) at 66MHz and 10mA(max.) at 33MHz
 - Low active programming current: 20mA (max.)
 - Low active erase current: 20mA (max.)
 - Low standby current: 20uA (max.)
 - Deep power-down mode 1uA (typical)
- Typical 100,000 erase/program cycles

SOFTWARE FEATURES

- Input Data Format
 - 1-byte Command code
- Advanced Security Features
 - Block lock protection
 - The BP0-BP3 status bit defines the size of the area to be software protection against program and erase instructions
 - Additional 512-bit secured OTP for unique identifier
- Auto Erase and Auto Program Algorithm
 - Automatically erases and verifies data at selected sector
 - Automatically programs and verifies data at selected page by an internal algorithm that automatically times the program pulse widths (Any page to be programed should have page in the erased state first)



- Status Register Feature
- Electronic Identification
 - JEDEC 1-byte manufacturer ID and 2-byte device ID
 - RES command for 1-byte Device ID
 - Both REMS and REMS2 commands for 1-byte manufacturer ID and 1-byte device ID

HARDWARE FEATURES

- SCLK Input
 - Serial clock input
- SI Input
 - Serial Data Input
- SO Output
 - Serial Data Output
- WP#/ACC pin
 - Hardware write protection and program/erase acceleration
- HOLD# pin
 - pause the chip without diselecting the chip
- PACKAGE
 - 16-pin SOP (300mil)
 - 8-land WSON (8x6mm or 6x5mm)
 - 8-pin SOP (200mil, 150mil)
 - 8-pin PDIP (300mil)
 - 8-land USON (4x4mm)
 - All Pb-free devices are RoHS Compliant

ALTERNATIVE

Security Serial Flash (MX25L1615D/MX25L3215D/MX25L6415D) may provides additional protection features for option. The datasheet is provided under NDA.

GENERAL DESCRIPTION

The MX25L1605D are 16,777,216 bit serial Flash memory, which is configured as $2,097,152 \times 8$ internally. When it is in two I/O read mode, the structure becomes 8,388,608 bits x 2. The MX25L3205D are 33,554,432 bit serial Flash memory, which is configured as $4,194,304 \times 8$ internally. When it is in two I/O read mode, the structure becomes 16,772,216 bits x 2. The MX25L6405D are 67,108,864 bit serial Flash memory, which is configured as $8,388,608 \times 8$ internally. When it is in two I/O read mode, the structure becomes 33,554,432 bits x 2. (please refer to the "Two I/O Read mode" section). The MX25L1605D/3205D/6405D feature a serial peripheral interface and software protocol allowing operation on a simple 3-wire bus. The three bus signals are a clock input (SCLK), a serial data input (SI), and a serial data output (SO). Serial access to the device is enabled by CS# input.

When it is in two I/O read mode, the SI pin and SO pin become SIO0 pin and SIO1 pin for address/dummy bits input and data output.

The MX25L1605D/3205D/6405D provides sequential read operation on whole chip.

After program/erase command is issued, auto program/ erase algorithms which program/ erase and verify the specified page or sector/block locations will be executed. Program command is executed on byte basis, or page (256 bytes) basis, or word basis for Continuously program mode, and erase command is executes on sector (4K-byte), or block (64K-byte), or whole chip basis.

To provide user with ease of interface, a status register is included to indicate the status of the chip. The status read command can be issued to detect completion status of a program or erase operation via WIP bit.

Advanced security features enhance the protection and security functions, please see security features section for more details.

When the device is not in operation and CS# is high, it is put in standby mode and draws less than 20uA DC current.

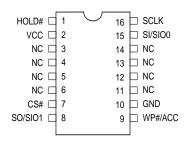
The MX25L1605D/3205D/6405D utilizes MXIC's proprietary memory cell, which reliably stores memory contents even after typical 100,000 program and erase cycles.

Table 1. Additional Feature Comparison

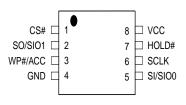
Additional	Protection and Security		Read Performance	Identifier			
Featu- res Part Name	Flexible Block protection (BP0-BP3)	512-bit secured OTP	2 I/O Read (50MHz)	Device ID (command : AB hex)	Device ID (command : 90 hex)	Device ID (command : EF hex)	RDID (command: 9F hex)
MX25L1605D	V	٧	٧	14 (hex)	C2 14 (hex) (if ADD=0)	C2 14 (hex) (if ADD=0)	C2 20 15 (hex)
MX25L3205D	٧	٧	٧	15 (hex)	C2 15 (hex) (if ADD=0)	C2 15 (hex) (if ADD=0)	C2 20 16 (hex)
MX25L6405D	V	V	V	16 (hex)	C2 16 (hex) (if ADD=0)	C2 16 (hex) (if ADD=0)	C2 20 17 (hex)

PIN CONFIGURATIONS

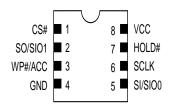
16-PIN SOP (300mil)



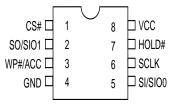
8-PIN SOP (200mil, 150mil)



8-LAND WSON (8x6mm, 6x5mm), USON (4x4mm)



8-PIN PDIP (300mil)



PACKAGE OPTIONS

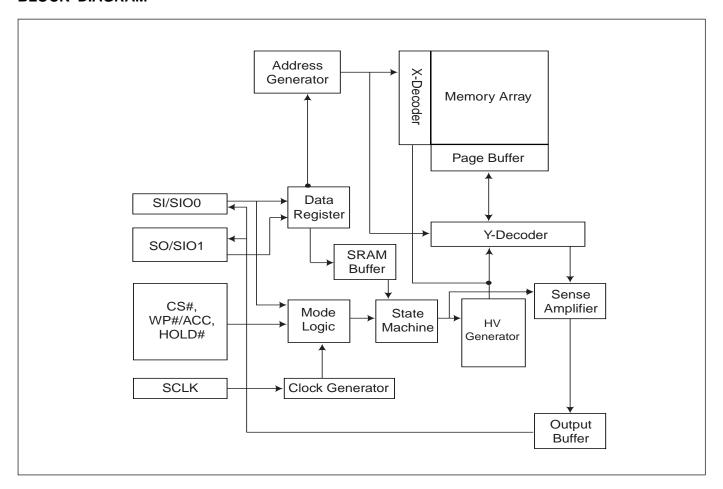
	16M	32M	64M
150mil 8-SOP	V		
200mil 8-SOP	V	V	
300mil 16-SOP	V	V	V
300mil8-PDIP	V	V	
6x5mmWSON	V	V	
8x6mmWSON			V
4x4mm USON	V	V	

PIN DESCRIPTION

SYMBOL	DESCRIPTION
- STWIDOL	DESCRIPTION
CS#	Chip Select
SI/SIO0	Serial Data Input (for 1 x I/O)/ Serial Data
	Input & Output (for 2xI/O read mode)
SO/SIO1	Serial Data Output (for 1 x I/O)/ Serial
	Data Input & Output (for 2xI/O read mode)
SCLK	Clock Input
WP#/ACC	Write protection: connect to GND;
	9.5~10.5V for program/erase
	acceleration: connect to 9.5~10.5V
HOLD#	Hold, to pause the device without
	deselecting the device
VCC	+ 3.3V Power Supply
GND	Ground



BLOCK DIAGRAM



DATA PROTECTION

The MX25L1605D/3205D/6405D is designed to offer protection against accidental erasure or programming caused by spurious system level signals that may exist during power transition. During power up the device automatically resets the state machine in the Read mode. In addition, with its control register architecture, alteration of the memory contents only occurs after successful completion of specific command sequences. The device also incorporates several features to prevent inadvertent write cycles resulting from VCC power-up and power-down transition or system noise.

- Power-on reset and tPUW: to avoid sudden power switch by system power supply transition, the power-on reset and tPUW (internal timer) may protect the Flash.
- Valid command length checking: The command length will be checked whether it is at byte base and completed on byte boundary.
- Write Enable (WREN) command: WREN command is required to set the Write Enable Latch bit (WEL) before other command to change data. The WEL bit will return to reset stage under following situation:
 - -Power-up
 - Write Disable (WRDI) command completion
 - Write Status Register (WRSR) command completion
 - Page Program (PP) command completion
 - Continuously Program mode (CP) instruction completion
 - Sector Erase (SE) command completion
 - Block Erase (BE) command completion
 - Chip Erase (CE) command completion
 - Write Read-lock Bit (WRLB) instruction completion
- Deep Power Down Mode: By entering deep power down mode, the flash device also is under protected from writing all commands except Release from deep power down mode command (RDP) and Read Electronic Signature command (RES).
- Advanced Security Features: there are some protection and securuity features which protect content from inadvertent
 write and hostile access.

I. Block lock protection

- The Software Protected Mode (SPM) use (BP3, BP2, BP1, BP0) bits to allow part of memory to be protected as read only. The proected area definition is shown as table of "Protected Area Sizes", the protected areas are more flexible which may protect various area by setting value of BP0-BP3 bits.
- Please refer to table of "protected area sizes".
- The Hardware Proteced Mode (HPM) use WP#/ACC to protect the (BP3, BP2, BP1, BP0) bits and SRWD bit.

Table 2. Protected Area Sizes

	Statu	s bit			Protect Level				
BP3	BP2	BP1	BP0	16Mb	32Mb	64Mb			
0	0	0	0	0(none)	O(none)	0(none)			
0	0	0	1	1(1block, block 31th)	1(1block, block 63th)	1(2blocks, block 126th-127th)			
0	0	1	0	2(2blocks, block 30th-31th)	2(2blocks, block 62th-63th)	2(4blocks, block 124th-127th)			
0	0	1	1	3(4blocks, block 28th-31th)	3(4blocks, block 60th-63th)	3(8blocks, block 120th-127th)			
0	1	0	0	4(8blocks, block 24th-31th)	4(8blocks, block 56th-63th)	4(16blocks, block 112th-127th)			
0	1	0	1	5(16blocks, block 16th-31th)	5(16blocks, block 48th-63th)	5(32blocks, block 96th-127th)			
0	1	1	0	6(32blocks, all)	6(32blocks, block 32th-63th)	6(64blocks,block 64th-127th)			
0	1	1	1	7(32blocks, all)	7(64blocks, all)	7(128blocks, all)			
1	0	0	0	8(32blocks, all)	8(64blocks, all)	8(128blocks, all)			
1	0	0	1	9(32blocks, all)	9(32blocks, block 0th-31th)	9(64blocks, block 0th-63th)			
1	0	1	0	10(16blocks, block 0th-15th)	10(48blocks, block 0th-47th)	10(96blocks, block 0th-95th)			
1	0	1	1	11(24blocks, block 0th-23th)	11(56blocks, block 0th-55th)	11(112blocks, block 0th-111th)			
1	1	0	0	12(28blocks, block 0th-27th)	12(60blocks, block 0th-59th)	12(120blocks, block 0th-119th)			
1	1	0	1	13(30blocks, block 0th-29th)	13(62blocks, block 0th-61th)	13(124blocks, block 0th-123th)			
1	1	1	0	14(31blocks, block 0th-30th)	14(63blocks, block 0th-62th)	14(126blocks, block 0th-125th)			
1	1	1	1	15(32blocks, all)	15(64blocks, all)	15(128blocks, all)			

II. Additional 512-bit secured OTP for unique identifier: to provide 512-bit one-time program area for setting device unique serial number - Which may be set by factory or system customer. Please refer to table 3. 512-bit secured OTP definition.

- Security register bit 0 indicates whether the chip is locked by factory or not.
- To program the 512-bit secured OTP by entering 512-bit secured OTP mode (with ENSO command), and going through normal program procedure, and then exiting 512-bit secured OTP mode by writing EXSO command.
- Customer may lock-down the customer lockable secured OTP by writing WRSCUR (write security register) command to set customer lock-down bit1 as "1". Please refer to table of "security register definition" for security register bit definition and table of "512-bit secured OTP definition" for address range definition.
- Note: Once lock-down whatever by factory or customer, it cannot be changed any more. While in 512-bit secured OTP mode, array access is not allowed.

Table 3. 512-bit Secured OTP Definition

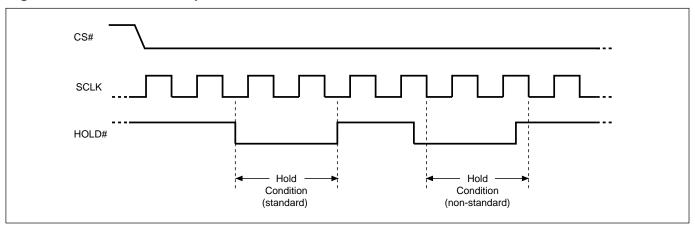
Address range	Size	Standard	Customer Lock	
		Factory Lock		
xxxx00~xxxx0F	128-bit	ESN (electrical serial number)		
40 05	00411		 Determined by customer 	
xxxx10~xxxx3F	384-bit	N/A		

HOLD FEATURES

HOLD# pin signal goes low to hold any serial communications with the device. The HOLD feature will not stop the operation of write status register, programming, or erasing in progress.

The operation of HOLD requires Chip Select(CS#) keeping low and starts on falling edge of HOLD# pin signal while Serial Clock (SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not start until Serial Clock signal being low). The HOLD condition ends on the rising edge of HOLD# pin signal while Serial Clock(SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not end until Serial Clock being low), see Figure 1.

Figure 1. Hold Condition Operation



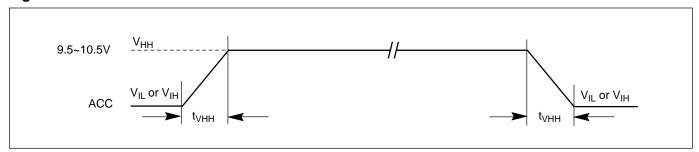
The Serial Data Output (SO) is high impedance, both Serial Data Input (SI) and Serial Clock (SCLK) are don't care during the HOLD operation. If Chip Select (CS#) drives high during HOLD operation, it will reset the internal logic of the device. To re-start communication with chip, the HOLD# must be at high and CS# must be at low.

PROGRAM/ERASE ACCELERATION

To activate the program/erase acceleration function requires ACC pin connecting to 9.5~10.5V voltage (see Figure 2), and then to be followed by the normal program/erase process. By utilizing the program/erase acceleration operation, the performances are improved as shown on table of "ERASE AND PROGRAM PERFORMACE".

After power-up ready, it should wait 10ms at least to apply VHH(9.5~10.5V) on the WP#/ACC pin.

Figure 2. ACCELERATED PROGRAM TIMING DIAGRAM



Note: tVHH (VHH Rise and Fall Time) min. 250ns



Table 4. COMMAND DEFINITION

COMMAND	WREN	WRDI	RDID (read	RDSR	WRSR	READ	FAST	2READ (2	SE (sector
(byte)	(write	(write	identification	(read	(write	(read data)	READ	x I/O read	erase)
	enable)	disable))	status	status		(fast read	command)	
				register)	register)		data)	note1	
1st byte	06 (hex)	04 (hex)	9F (hex)	05 (hex)	01 (hex)	03 (hex)	0B (hex)	BB (hex)	20 (hex)
2nd byte						AD1	AD1	ADD(2)	AD1
3rd byte						AD2	AD2	ADD(2) &	AD2
								Dummy(2)	
4th byte						AD3	AD3		AD3
5th byte							Dummy		
Action	sets the	resets the		to read out		n bytes	n bytes	,	to erase
	(WEL)	(WEL)			new values		read out		the
	write	write	1-byte	of the	to the	until CS#	until CS#	by 2 x I/O	selected
	enable	enable	manufactur	status	status	goes high	goes high	until CS#	sector
	latch bit	latch bit	er ID & 2-	register	register			goes high	
			byte device						
			ID	(5) 1				01/0100	

Note 1: The count base is 4-bit for ADD(2) and Dummy(2) because of 2 x I/O. And the MSB is on SI/SIO0 which is different from 1 x I/O condition

			1	1					
COMMAND	BE (block	CE (chip	PP (Page	CP	DP (Deep	RDP	RES (read	REMS	REMS2
(byte)	erase)	erase)	program)	(Continuo-	power	(Release	electronic	(read	(read ID
				usly	down)	from deep	ID)	electronic	for 2x I/O
				program		power		manufactu-	mode)
				mode)		down)		rer &	
								device ID)	
1st byte	D8 (hex)	60 or C7 (hex)	02 (hex)	AD (hex)	B9 (hex)	AB (hex)	AB (hex)	90 (hex)	EF (hex)
2nd byte	AD1		AD1	AD1			х	х	х
3rd byte	AD2		AD2	AD2			х	х	х
4th byte	AD3		AD3	AD3			х	ADD(note	ADD(note
-								2)	2)
5th byte									
Action	to erase	to erase	to program	continously	enters	release	to read out	outout the	output the
	the	whole chip	the selected	program	deep	from deep	1-byte	manufactu-	manufactu-
	selected		page	whole	power	power	device ID	rer ID &	rer ID &
	block			chip, the	down	down		device ID	device ID
				address is	mode	mode			
				automatica					
				lly increase					

Note 2: ADD=00H will output the manufacturer ID first and ADD=01H will output device ID first

COMMAND	ENSO	EXSO	RDSCUR	WRSCUR	ESRY	DSRY
(byte)	(enter	(exit	(read	(write	(enable	(disable
	secured	secured	security	security	SO to	SO to
	OTP)	OTP)	register)	register)	output	output
					RY/BY#)	RY/BY#)
1st byte	B1 (hex)	C1 (hex)	2B (hex)	2F (hex)	70 (hex)	80 (hex)
2nd byte						
3rd byte						
4th byte						
5th byte						
Action	to enter the 512-bit secured OTP mode	to exit the 512-bit secured OTP mode	to read value of security register	to set the lock-down bit as "1" (once lock- down, cannot be updated)	to enable SO to output RY/BY# during CP mode	to disable SO to output RY/BY# during CP mode

Note 3: It is not recommoded to adopt any other code not in the command definition table, which will potentially enter the hidden mode.



Table 5-1. Memory Organization (16Mb)

Block	Sector	Addres	s Range
DIOCK	511	1FF000h	1FFFFFh
31	:	:	:
0.1	496	1F0000h	: 1F0FFFh
	495	1EF000h	1EFFFFh
30	495	12500011	
30	: 400	:	:
	480 479	1E0000h	1E0FFFh 1DFFFFh
29	479	1DF000h	IDFFFFII
23	:	: 4D0000b	:
	464	1D0000h	1D0FFFh 1CFFFFh
28	463	1CF000h	·
20	:	:	:
	448	1C0000h	1C0FFFh
07	447	1BF000h	1BFFFFh
27	<u>:</u>	:	:
	432	1B0000h	1B0FFFh
	431	1AF000h	1AFFFFh
26	:	:	:
	416	1A0000h	1A0FFFh
	415	19F000h	19FFFFh
25	:	:	:
	400	190000h	190FFFh
	399	18F000h	18FFFFh
24	:	:	:
	384	180000h	180FFFh
	383	17F000h	17FFFFh
23	:	:	:
	368	170000h	170FFFh
22	367	16F000h	16FFFFh
22	:		:
	352	160000h	160FFFh
0.4	351	15F000h	15FFFFh
21	:	:	:
	336	150000h	150FFFh
	335	14F000h	14FFFFh
20	<u> </u>	:	:
	320	140000h	140FFFh
	319	13F000h	13FFFFh
19		<u> </u>	<u> </u>
	304	130000h	130FFFh
	303	12F000h	12FFFFh
18	:	:	:
	288	120000h	120FFFh
	287	11F000h	11FFFFh
17	:	:	:
•	272	110000h	110FFFh
	271	10F000h	10FFFFh
16			
'	: 256	1000006	1005556
	256	100000h	100FFFh

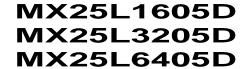
Block	Sector	Addres	s Range
	255	0FF000h	0FFFFFh
15	:	:	:
	240	0F0000h	0F0FFFh
	239	0EF000h	0EFFFFh
14	:	:	:
14	224	0E0000h	0E0FFFh
	223	0DF000h	0DFFFFh
13	:	:	:
	208	0D0000h	0D0FFFh
	207	0CF000h	0CFFFFh
12	:	:	:
	192	0C0000h	0C0FFFh
	191	0BF000h	0BFFFFh
11	:	:	:
	176	0B0000h	0B0FFFh
	175	0AF000h	0AFFFFh
10	175	:	:
	160	0A0000h	OA0FFFh
-	159	09F000h	09FFFFh
9	159		U9FFFFN
9	:	:	:
	144	090000h	090FFFh
	143	08F000h	08FFFFh
8	<u>:</u>	:	:
	128	080000h	080FFFh
_	127	07F000h	07FFFFh
7	:	:	:
	112	070000h	070FFFh
	111	06F000h	06FFFFh
6		l :	:
	96	060000h	060FFFh
	95	05F000h	05FFFFh
5	:	:	:
	80	050000h	050FFFh
	79	04F000h	04FFFFh
4	÷.	÷	÷
	64	040000h	040FFFh
	63	03F000h	03FFFFh
3	:	:	:
L_	48	030000h	030FFFh
	47	02F000h	02FFFFh
2	- '' :	:	:
	32	020000h	020FFFh
	31	01F000h	01FFFFh
1	31	:	:
'	: 16	: 010000h	: 010FFFh
-	15	00F000h	00FFFFh
	- 13		
	<u>:</u> 4	0040006	: 004FFFh
0	3	004000h	004FFFh 003FFFh
	2	003000h	003FFFh 002FFFh
	1	002000h	002FFFN 001FFFh
		001000h	001FFFh 000FFFh
	0	000000h	UUUFFN



Table 5-2. Memory Organization (32Mb)

Block	Sector	Address Range				
	1023	3FF000h	3FFFFFh			
63		:	:			
	1008	3F0000h	3F0FFFh			
	1007	3EF000h	3EFFFFh			
62	<u> </u>	:	:			
	992	3E0000h	3E0FFFh			
	991	3DF000h	3DFFFFh			
61	<u> </u>	:	:			
	976	3D0000h	3D0FFFh			
	975	3CF000h	3CFFFFh			
60	:	:	i i			
	960	3C0000h	3C0FFFh			
	959	3BF000h	3BFFFFh			
59		:	:			
	944	3B0000h	3B0FFFh			
	943	3AF000h	3AFFFFh			
58	:	:	:			
	928	3A0000h	3A0FFFh			
	927	39F000h	39FFFFh			
57	:	:	:			
	912	390000h	390FFFh			
	911	38F000h	38FFFFh			
56	:	:	:			
	896	380000h	380FFFh			
	895	37F000h	37FFFFh			
55	:	:	:			
	880	370000h	370FFFh			
54	879	36F000h	36FFFFh			
34	:	:	:			
	864	360000h	360FFFh			
50	863	35F000h	35FFFFh			
53	<u>:</u>	:	:			
	848	350000h	350FFFh			
50	847	34F000h	34FFFFh			
52	<u> </u>	:	:			
	832	340000h	340FFFh			
	831	33F000h	33FFFFh			
51	<u> </u>	:	:			
	816	330000h	330FFFh			
	815	32F000h	32FFFFh			
50	:	:	:			
	800	320000h	320FFFh			
	799	31F000h	31FFFFh			
49	:	:	:			
	784	310000h	310FFFh			
	783	30F000h	30FFFFh			
48	:	:	:			
	768	300000h	300FFFh			
	, , , , ,	1 00000011	1 00011111			

Block	Sector	Address	s Range
	767	2FF000h	2FFFFFh
47	:	:	:
	752	2F0000h	2F0FFFh
	751	2EF000h	2EFFFFh
46	:	:	÷
46	736	2E0000h	2E0FFFh
	735	2DF000h	2DFFFFh
45	i i		÷
	720	2D0000h	2D0FFFh
	719	2CF000h	2CFFFFh
44	:	:	:
	704	2C0000h	2C0FFFh
	703	2BF000h	2BFFFFh
43	:	:	:
	688	2B0000h	2B0FFFh
	687	2AF000h	2AFFFFh
42	:	:	:
	672	2A0000h	2A0FFFh
	671	29F000h	29FFFFh
41	- 671	29F00011	. 29FFFFII
~'	<u>:</u> 656	: 200000h	: 290FFFh
		290000h	
40	655	28F000h	28FFFFh
40	:	:	:
	640	280000h	280FFFh
20	639	27F000h	27FFFFh
39	:	:	:
	624	270000h	270FFFh
	623	26F000h	26FFFFh
38		i i	i
	608	260000h	260FFFh
	607	25F000h	25FFFFh
37	:	:	:
	592	250000h	250FFFh
	591	24F000h	24FFFFh
36	:	:	:
	576	240000h	240FFFh
	575	23F000h	23FFFFh
35	:	:	:
<u> </u>	560	230000h	230FFFh
	559	22F000h	22FFFFh
34	:	:	:
ĺ	<u>.</u> 544	220000h	220FFFh
	543	21F000h	21FFFFh
33	:	:	;
	528	: 210000h	: 210FFFh
 	527	20F000h	20FFFFh
32	. 521	20100011	- ZUI-FFFII -
] 32	<u>:</u>	:	:
	512	200000h	200FFFh





Block	Sector	Addres	s Range
	511	1FF000h	1FFFFFh
31	:	:	:
	496	1F0000h	1F0FFFh
	495	1EF000h	1EFFFFh
30	:	:	:
	480	1E0000h	1E0FFFh
	479	1DF000h	1DFFFFh
29	:	:	:
	464	1D0000h	1D0FFFh
	463	1CF000h	1CFFFFh
28	:	:	:
	448	1C0000h	1C0FFFh
	447	1BF000h	1BFFFFh
27	:	:	:
	432	1B0000h	1B0FFFh
	431	1AF000h	1AFFFFh
26	:	:	:
	416	1A0000h	1A0FFFh
	415	19F000h	19FFFFh
25	:	:	:
20	400	: 190000h	: 190FFFh
	399	18F000h	
24	. 399		18FFFFh
24	384	: 100000h	: 100FFFb
		180000h	180FFFh 17FFFFh
23	383	17F000h	
25	:	: 470000b	: 470555
	368	170000h	170FFFh
00	367	16F000h	16FFFFh
22	<u> </u>	:	:
	352	160000h	160FFFh
	351	15F000h	15FFFFh
21		:	:
	336	150000h	150FFFh
	335	14F000h	14FFFFh
20	<u> </u>	:	:
	320	140000h	140FFFh
	319	13F000h	13FFFFh
19	<u> </u>	:	:
	304	130000h	130FFFh
	303	12F000h	12FFFFh
18	:	:	i i
	288	120000h	120FFFh
	287	11F000h	11FFFFh
17	:	:	:
	272	110000h	110FFFh
	271	10F000h	10FFFFh
16	:	:	:
	256	100000h	100FFFh
		10000011	10011111

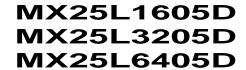
Block	Sector	Addres	s Range
	255	0FF000h	0FFFFFh
15	:	:	:
	240	0F0000h	0F0FFFh
	239	0EF000h	0EFFFFh
14	- 200	· ·	·
'~	224	:	:
		0E0000h	0E0FFFh
13	223	0DF000h	0DFFFFh
13	:	:	:
	208	0D0000h	0D0FFFh
	207	0CF000h	0CFFFFh
12	<u> </u>	<u> </u>	:
	192	0C0000h	0C0FFFh
	191	0BF000h	0BFFFFh
11	:	:	:
	176	0B0000h	0B0FFFh
	175	0AF000h	0AFFFFh
10	- '''	•	•
I 'Ŭ	100	:	:
<u> </u>	160	0A0000h	0A0FFFh
	159	09F000h	09FFFFh
9	l :	:	:
	144	090000h	090FFFh
	143	08F000h	08FFFFh
8	:	:	:
	128	080000h	080FFFh
	127	07F000h	07FFFFh
7	:	:	:
·	112	070000h	070FFFh
	111	06F000h	06FFFFh
6	<u> </u>	ļ :	:
	96	060000h	060FFFh
	95	05F000h	05FFFFh
5	:	:	:
	80	050000h	050FFFh
	79	04F000h	04FFFFh
4	:	:	:
· .	64	: 040000h	: 040FFFh
-			
2	63	03F000h	03FFFFh
3	:	:	:
<u> </u>	48	030000h	030FFFh
	47	02F000h	02FFFFh
2			
	32	020000h	020FFFh
	31	01F000h	01FFFFh
1	:	:	:
l '		1 0100006	
	16	010000h	010FFFh
	15	00F000h	00FFFFh
		<u> </u>	<u> </u>
	4	004000h	004FFFh
0	3	003000h	003FFFh
	2	002000h	002FFFh
	1	001000h	001FFFh
	0	000000h	000FFFh



Table 5-3. Memory Organization (64Mb)

Block	Sector	Address	s Range
	2047	7FF000h	7FFFFFh
127	:	:	:
	2032	7F0000h	7F0FFFh
	2031	7EF000h	7EFFFFh
126	:	:	:
	2016	7E0000h	7E0FFFh
	2015	7DF000h	7DFFFFh
125	:	:	:
	2000	7D0000h	7D0FFFh
	1999	7CF000h	7CFFFFh
124	:	:	:
	1984	7C0000h	7C0FFFh
	1983	7BF000h	7BFFFFh
123	:	:	:
	 1968	7B0000h	7B0FFFh
	1967	7AF000h	7AFFFFh
122	:	:	: :
	1952	7A0000h	; 7A0FFFh
121	1951	79F000h	79FFFFh
121	:	:	:
	1936	790000h	790FFFh
400	1935	78F000h	78FFFFh
120	:	:	:
	1920	780000h	780FFFh
110	1919	77F000h	77FFFFh
119	:	:	<u>:</u>
	1904	770000h	770FFFh
	1903	76F000h	76FFFFh
118	:	:	:
	1888	760000h	760FFFh
	1887	75F000h	75FFFFh
117	:	:	:
	1872	750000h	750FFFh
	1871	74F000h	74FFFFh
116	:	:	:
	1856	740000h	740FFFh
	1855	73F000h	73FFFFh
115	:	:	:
L	1840	730000h	730FFFh
	1839	72F000h	72FFFFh
114	:	:	:
	<u>.</u> 1824	720000h	720FFFh
	1823	71F000h	71FFFFh
113	:	:	:
	1808	: 710000h	: 710FFFh
	1807	70F000h	70FFFh
112	. 1007		/ VI-FFFII
' ' ~	: 1792	: 700000h	: 700FFFh
	1792	70000011	/00///

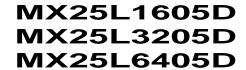
Block	Sector	Address	s Range
	1791	6FF000h	6FFFFFh
111	:	:	:
	1776	6F0000h	6F0FFFh
	1775	6EF000h	6EFFFFh
110	:	:	:
	1760	6E0000h	6E0FFFh
	1759	6DF000h	6DFFFFh
109	:	:	i
	1744	6D0000h	6D0FFFh
400	1743	6CF000h	6CFFFFh
108	<u>:</u>	:	:
	1728	6C0000h	6C0FFFh
	1727	6BF000h	6BFFFFh
107	<u> </u>	:	:
	1712	6B0000h	6B0FFFh
	1711	6AF000h	6AFFFFh
106	:	:	:
	1696	6A0000h	6A0FFFh
	1695	69F000h	69FFFFh
105	:	:	:
	1680	690000h	690FFFh
	1679	68F000h	68FFFFh
104	:	:	:
	1664	680000h	680FFFh
	1663	67F000h	67FFFFh
103	:	:	:
	1648	670000h	670FFFh
	1647	66F000h	66FFFFh
102	:	:	:
	1632	660000h	660FFFh
	1631	65F000h	65FFFFh
101	:	:	:
	1616	650000h	650FFFh
	1615	64F000h	64FFFFh
100	:	:	<u> </u>
	1600	640000h	640FFFh
	1599	63F000h	63FFFFh
99	:	:	:
	1584	630000h	630FFFh
	1583	62F000h	62FFFFh
98	:	:	:
	1568	620000h	620FFFh
	1567	61F000h	61FFFFh
97	:	:	:
	1552	610000h	610FFFh
	1551	60F000h	60FFFFh
96	:	:	:
ĺ	1536	600000h	600FFFh
			





Block	Sector	Addres	s Range
2.000	1535	5FF000h	5FFFFFh
95	:	:	:
	 1520	5F0000h	5F0FFFh
	1519	5EF000h	5EFFFFh
94		3EF00011	· ·
01	1504	: FE0000h	:
	1504 1503	5E0000h 5DF000h	5E0FFFh 5DFFFFh
93	1505	3DF00011	3DEFFEII
33	: 1488	5D0000h	: 5D0FFFh
	1487	5CF000h	5CFFFFh
92	:	301 00011	:
02	1472	5C0000h	: 5C0FFFh
	1472	5BF000h	5BFFFFh
91	1471	36700011	OBFFFFII
91	: 1450	: :	: CDOEFEL
	1456	5B0000h	5B0FFFh
00	1455	5AF000h	5AFFFFh
90	:	:	:
	1440	5A0000h	5A0FFFh
	1439	59F000h	59FFFFh
89	<u> </u>	<u> </u>	:
	1424	590000h	590FFFh
	1423	58F000h	58FFFFh
88			:
	1408	580000h	580FFFh
	1407	57F000h	57FFFFh
87			÷
	1392	570000h	570FFFh
	1391	56F000h	56FFFFh
86	:	:	:
	1376	560000h	560FFFh
	1375	55F000h	55FFFFh
85	:	:	:
	1360	550000h	550FFFh
	1359	54F000h	54FFFFh
84		:	:
	1344	540000h	540FFFh
	1343	53F000h	53FFFFh
83	:	:	:
	1328	530000h	530FFFh
	1327	52F000h	52FFFFh
82	:	:	:
- <u>-</u>	1312	520000h	: 520FFFh
	1312	51F000h	51FFFFh
81		31500011	JIFFFFII
	1206	5100006	: 510FFFh
	1296	510000h	
80	1295	50F000h	50FFFFh ·
80	: 4000	:	:
	1280	500000h	500FFFh

Block	Sector	Address	s Range
	1279	4FF000h	4FFFFFh
79	:	:	:
	1264	4F0000h	4F0FFFh
	1263	4EF000h	4EFFFFh
78	:	:	:
	1248	4E0000h	4E0FFFh
	1247	4DF000h	4DFFFFh
77	:	:	:
	1232	4D0000h	4D0FFFh
	1231	4CF000h	4CFFFFh
76	:	:	:
	1216	4C0000h	4C0FFFh
	1215	4BF000h	4BFFFFh
75	:	:	:
	1200	4B0000h	4B0FFFh
	1119	4AF000h	4AFFFFh
74	1 :	:	:
	1184	4A0000h	4A0FFFh
	1183	49F000h	49FFFFh
73	1103	491 00011	
'	: 1168	: 490000h	: 490FFFh
	1167		
72		48F000h	48FFFFh
12	:		:
	1152 1151	480000h	480FFFh
71	1151	47F000h	47FFFFh
'	: 4420	: 470000b	:
	1136	470000h	470FFFh
	1135	46F000h	46FFFFh
70	:	:	:
	1120	460000h	460FFFh
	1119	45F000h	45FFFFh
69		<u> </u>	i i
	1104	450000h	450FFFh
	1103	44F000h	44FFFFh
68	:	:	:
	1088	440000h	440FFFh
	1087	43F000h	43FFFFh
67	:	:	
	1072	430000h	430FFFh
	1071	42F000h	42FFFFh
66	:	:	:
	1056	420000h	420FFFh
	1055	41F000h	41FFFFh
65	:	:	:
	1040	410000h	: 410FFFh
	1039	40F000h	40FFFFh
64	:	+01 00011	 0111FII
~	1024	1000006	: 400EEE
	1024	400000h	400FFFh





Block	Sector	Addres	s Range
2.001	1023	3FF000h	3FFFFFh
63	:	:	:
	1008	3F0000h	3F0FFFh
	1007	3EF000h	3EFFFFh
62	1007	3EF00011	· ·
02	:	:	:
	992 991	3E0000h 3DF000h	3E0FFFh 3DFFFFh
61	991	3DF000h	3DFFFFN
01	:	:	:
	976	3D0000h	3D0FFFh
00	975	3CF000h	3CFFFFh
60	:	:	:
	960	3C0000h	3C0FFFh
	959	3BF000h	3BFFFFh
59	:	<u> </u>	:
	944	3B0000h	3B0FFFh
	943	3AF000h	3AFFFFh
58	:	:	
	928	3A0000h	3A0FFFh
	927	39F000h	39FFFFh
57	:	:	:
	912	390000h	390FFFh
	911	38F000h	38FFFFh
56			
00	: :	3900006	300EEE
	896	380000h	380FFFh
55	895	37F000h	37FFFFh
55	:	:	:
	880	370000h	370FFFh
	879	36F000h	36FFFFh
54	:	:	:
	864	360000h	360FFFh
	863	35F000h	35FFFFh
53	:	:	:
	848	350000h	350FFFh
	847	34F000h	34FFFFh
52	:	:	:
	832	340000h	340FFFh
	831	33F000h	33FFFFh
51	:	:	:
	216	3300004	: 330FFFh
	816	330000h	
5 0	815	32F000h	32FFFFh
50	<u> </u>	<u> </u>	
	800	320000h	320FFFh
	799	31F000h	31FFFFh
49	:	:	
	784	310000h	310FFFh
	783	30F000h	30FFFFh
48	:	:	:
	 768	300000h	300FFFh
	7.00	JUUUUUII	00011111

Block	Sector	Address Range			
DIOCK	767	2FF000h	2FFFFFh		
47	:	:	:		
	752	2F0000h	2F0FFFh		
	 				
46	751 ·	2EF000h	2EFFFFh		
40	<u> </u>	:	:		
	736	2E0000h	2E0FFFh		
4-	735	2DF000h	2DFFFFh		
45	:	:	:		
	720	2D0000h	2D0FFFh		
	719	2CF000h	2CFFFFh		
44	<u> </u>	:	:		
	704	2C0000h	2C0FFFh		
	703	2BF000h	2BFFFFh		
43	:	:	:		
	688	2B0000h	2B0FFFh		
	687	2AF000h	2AFFFFh		
42					
72	:	:	:		
	672	2A0000h	2A0FFFh		
	671	29F000h	29FFFFh		
41	:	:	:		
	656	290000h	290FFFh		
	655	28F000h	28FFFFh		
40	:	:	:		
	640	280000h	280FFFh		
	639	27F000h	27FFFFh		
39	:	:	:		
	624	270000h	270FFFh		
	623	26F000h	26FFFFh		
38		:			
	608	260000h	260FFFh		
	607	25F000h	25FFFFh		
37	:	i i	:		
	592	250000h	250FFFh		
	591	24F000h	24FFFFh		
36	:	:	:		
	576	240000h	240FFFh		
	575	23F000h	23FFFFh		
35	:	:	:		
	<u>:</u>	3300006	: 230FFFh		
	560	230000h			
<u> </u>	559	22F000h	22FFFFh		
34	<u> </u>	:	<u> </u>		
	544	220000h	220FFFh		
	543	21F000h	21FFFFh		
33	:	:	:		
	528	210000h	210FFFh		
	527	20F000h	20FFFFh		
32	:	:	:		
	512	: 200000h	200FFFh		
	012	20000011	20077711		





Block	Sector	Address Range			
DIOCK	511	1FF000h	1FFFFFh		
31	:	:	:		
	496	1F0000h	1F0FFFh		
	495	1EF000h	1EFFFFh		
30	:	:	:		
	480	1E0000h	1E0FFFh		
	479	1DF000h	1DFFFFh		
29	:	:	:		
	464	1D0000h	1D0FFFh		
	463	1CF000h	1CFFFFh		
28	:	:	:		
	448	1C0000h	1C0FFFh		
	447	1BF000h	1BFFFFh		
27	:	101 00011	:		
l -'	432	: 1B0000h	: 1B0FFFh		
			1AFFFFh		
26	431	1AF000h	IAFFFN		
20	:	:	:		
	416	1A0000h	1A0FFFh		
0.5	415	19F000h	19FFFFh		
25	<u> </u>	:	:		
	400	190000h	190FFFh		
	399	18F000h	18FFFFh		
24	<u> </u>	:	:		
	384	180000h	180FFFh		
	383	17F000h	17FFFFh		
23	<u> </u>	:	:		
	368	170000h	170FFFh		
	367	16F000h	16FFFFh		
22	:	:	:		
	352	160000h	160FFFh		
	351	15F000h	15FFFFh		
21	:	:	:		
	336	150000h	150FFFh		
	335	14F000h	14FFFFh		
20	:	:	:		
	320	140000h	140FFFh		
	319	13F000h	13FFFFh		
19	:	:	:		
	304	130000h	130FFFh		
	303	12F000h	12FFFFh		
18	:	:	:		
	288	120000h	: 120FFFh		
	287	11F000h	11FFFFh		
17	- 201				
l ''	272	1100006	110555		
	272	110000h	110FFFh		
16	271	10F000h	10FFFFh		
10	:	1000001	:		
	256	100000h	100FFFh		

Block	Sector	Addres	s Range
Biook	255	0FF000h	0FFFFFh
15	- 255		
13	:	:	:
	240	0F0000h	0F0FFFh
	239	0EF000h	0EFFFFh
14	:		:
	224	0E0000h	0E0FFFh
	223	0DF000h	0DFFFFh
13	:	:	:
	208	0D0000h	0D0FFFh
	207	0CF000h	0CFFFFh
12	- 201		
12	:	:	:
	192	0C0000h	0C0FFFh
	191	0BF000h	0BFFFFh
11	:		:
	176	0B0000h	0B0FFFh
	175	0AF000h	0AFFFFh
10	:	:	:
	160	0A0000h	OA0FFFh
	159	09F000h	09FFFFh
9	<u> </u>	<u> </u>	:
	144	090000h	090FFFh
	143	08F000h	08FFFFh
8	:	:	:
	128	080000h	080FFFh
	127	07F000h	07FFFFh
7	127	•	•
,	: 440	:	:
	112	070000h	070FFFh
	111	06F000h	06FFFFh
6	:	l :	:
	96	060000h	060FFFh
	95	05F000h	05FFFFh
5	:	:	:
		0500006	050555
	80	050000h	050FFFh
_	79	04F000h	04FFFFh
4	<u> </u>		
	64	040000h	040FFFh
	63	03F000h	03FFFFh
3	<u> </u>	:	
	48	030000h	030FFFh
	47	02F000h	02FFFFh
2	'' .		
	:	:	:
	32	020000h	020FFFh
	31	01F000h	01FFFFh
1	: -	:	:
	16	010000h	010FFFh
	15	00F000h	00FFFFh
	:	:	:
	4	: 004000h	: 004FFFh
0			
U	3	003000h	003FFFh
	2	002000h	002FFFh
	1	001000h	001FFFh
I	0	000000h	000FFFh

DEVICE OPERATION

- 1. Before a command is issued, status register should be checked to ensure device is ready for the intended operation.
- 2. When incorrect command is inputted to this LSI, this LSI becomes standby mode and keeps the standby mode until next CS# falling edge. In standby mode, SO pin of this LSI should be High-Z.
- 3. When correct command is inputted to this LSI, this LSI becomes active mode and keeps the active mode until next CS# rising edge.
- 4. Input data is latched on the rising edge of Serial Clock(SCLK) and data shifts out on the falling edge of SCLK. The difference of Serial mode 0 and mode 3 is shown as Figure 3.
- 5. For the following instructions: RDID, RDSR, RDSCUR, READ, FAST_READ, 2READ, RES, REMS and REMS2 the shifted-in instruction sequence is followed by a data-out sequence. After any bit of data being shifted out, the CS# can be high. For the following instructions: WREN, WRDI, WRSR, SE, BE, CE, PP, CP, RDP, DP, ENSO, EXSO, and WRSCUR, the CS# must go high exactly at the byte boundary; otherwise, the instruction will be rejected and not executed.
- 6. During the progress of Write Status Register, Program, Erase operation, to access the memory array is neglected and not affect the current operation of Write Status Register, Program, Erase.

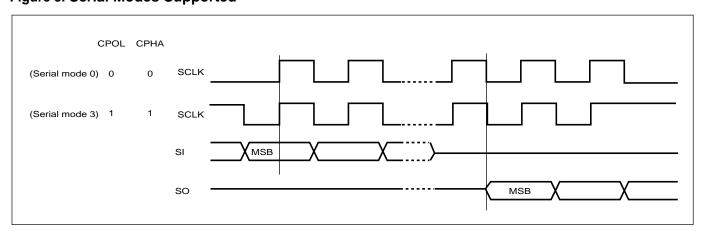


Figure 3. Serial Modes Supported

Note

CPOL indicates clock polarity of Serial master, CPOL=1 for SCLK high while idle, CPOL=0 for SCLK low while not transmitting. CPHA indicates clock phase. The combination of CPOL bit and CPHA bit decides which Serial mode is supported.



COMMAND DESCRIPTION

(1) Write Enable (WREN)

The Write Enable (WREN) instruction is for setting Write Enable Latch (WEL) bit. For those instructions like PP, CP, SE, BE, CE, and WRSR, which are intended to change the device content, should be set every time after the WREN instruction setting the WEL bit.

The sequence of issuing WREN instruction is: CS# goes low-> sending WREN instruction code-> CS# goes high. (see Figure 12)

(2) Write Disable (WRDI)

The Write Disable (WRDI) instruction is for resetting Write Enable Latch (WEL) bit.

The sequence of issuing WRDI instruction is: CS# goes low-> sending WRDI instruction code-> CS# goes high. (see Figure 13)

The WEL bit is reset by following situations:

- Power-up
- Write Disable (WRDI) instruction completion
- Write Status Register (WRSR) instruction completion
- Page Program (PP) instruction completion
- Sector Erase (SE) instruction completion
- Block Erase (BE) instruction completion
- Chip Erase (CE) instruction completion
- Continuously program mode (CP) instruction completion

(3) Read Identification (RDID)

The RDID instruction is for reading the manufacturer ID of 1-byte and followed by Device ID of 2-byte. The MXIC Manufacturer ID is C2(hex), the memory type ID is 20(hex) as the first-byte device ID, and the individual device ID of second-byte ID are listed as table of "ID Definitions".

The sequence of issuing RDID instruction is: CS# goes low-> sending RDID instruction code -> 24-bits ID data out on SO -> to end RDID operation can use CS# to high at any time during data out. (see Figure. 14)

While Program/Erase operation is in progress, it will not decode the RDID instruction, so there's no effect on the cycle of program/erase operation which is currently in progress. When CS# goes high, the device is at standby stage.

(4) Read Status Register (RDSR)

The RDSR instruction is for reading Status Register Bits. The Read Status Register can be read at any time (even in program/erase/write status register condition) and continuously. It is recommended to check the Write in Progress (WIP) bit before sending a new instruction when a program, erase, or write status register operation is in progress.

The sequence of issuing RDSR instruction is: CS# goes low-> sending RDSR instruction code-> Status Register data out on SO (see Figure. 15)

The definition of the status register bits is as below:

WIP bit. The Write in Progress (WIP) bit, a volatile bit, indicates whether the device is busy in program/erase/write status register progress. When WIP bit sets to 1, which means the device is busy in program/erase/write status register progress. When WIP bit sets to 0, which means the device is not in progress of program/erase/write status register cycle.

WEL bit. The Write Enable Latch (WEL) bit, a volatile bit, indicates whether the device is set to internal write enable latch. When WEL bit sets to 1, which means the internal write enable latch is set, the device can accept program/erase/write status register instruction. When WEL bit sets to 0, which means no internal write enable latch; the device will not accept program/erase/write status register instruction. The program/erase command will be ignored and not affect value of WEL bit if it is applied to a protected memory area.

BP3, BP2, BP1, BP0 bits. The Block Protect (BP3, BP2, BP1, BP0) bits, non-volatile bits, indicate the protected area (as defined in table 1) of the device to against the program/erase instruction without hardware protection mode being set. To write the Block Protect (BP3, BP2, BP1, BP0) bits requires the Write Status Register (WRSR) instruction to be executed. Those bits define the protected area of the memory to against Page Program (PP), Sector Erase (SE), Block Erase (BE) and Chip Erase(CE) instructions (only if all Block Protect bits set to 0, the CE instruction can be executed).

Continuously Program Mode (CP mode) bit. The Continuously Program Mode bit indicates the status of CP mode, "0" indicates not in CP mode; "1" indicates in CP mode.

SRWD bit. The Status Register Write Disable (SRWD) bit, non-volatile bit, is operated together with Write Protection (WP#/ACC) pin for providing hardware protection mode. The hardware protection mode requires SRWD sets to 1 and WP#/ACC pin signal is low stage. In the hardware protection mode, the Write Status Register (WRSR) instruction is no longer accepted for execution and the SRWD bit and Block Protect bits (BP3, BP2, BP1, BP0) are read only.

Status Register

bit7	bit6	bit5	bit4	bit3	bit2	bit1	bit0
SRWD	Continuously	BP3	BP2	BP1	BP0	WEL	WIP
(status register	program mode	(level of	(level of	(level of	(level of	(write enable	(write in
write protect)	(CP mode)	protected block)	protected block)	protected block)	protected block)	latch)	progress bit)
	0 = normal						1= write
1= status	program mode	(note1)	(note1)	(note1)	(note1)	1= write enable	operation
register write	1 = CP	(Hote I)	(Hote I)	(Hote I)	(Hote I)	0= not write	0= not in write
disable	mode(default 0)					enable	operation
Non-volatile bit	volatile bit	Non- volatile bit	Non-volatile bit	Non- volatile bit	Non- volatile bit	volatile bit	volatile bit

note1: see the table "Protected Area Sizes"

(5) Write Status Register (WRSR)

The WRSR instruction is for changing the values of Status Register Bits. Before sending WRSR instruction, the Write Enable (WREN) instruction must be decoded and executed to set the Write Enable Latch (WEL) bit in advance. The WRSR instruction can change the value of Block Protect (BP3, BP2, BP1, BP0) bits to define the protected area of memory (as shown in table 1). The WRSR also can set or reset the Status Register Write Disable (SRWD) bit in accordance with Write Protection (WP#/ACC) pin signal. The WRSR instruction cannot be executed once the Hardware Protected Mode (HPM) is entered.

The sequence of issuing WRSR instruction is: CS# goes low-> sending WRSR instruction code-> Status Register data on SI-> CS# goes high. (see Figure 16)

The WRSR instruction has no effect on b6, b1, b0 of the status register.

The CS# must go high exactly at the byte boundary; otherwise, the instruction will be rejected and not executed. The self-timed Write Status Register cycle time (tW) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be check out during the Write Status Register cycle is in progress. The WIP sets 1 during the tW timing, and sets 0 when Write Status Register Cycle is completed, and the Write Enable Latch (WEL) bit is reset.

Table 6. Protection Modes

Mode	Status register condition	WP# and SRWD bit status	Memory
Software protection mode(SPM)	Status register can be written in (WEL bit is set to "1") and the SRWD, BP0-BP3 bits can be changed	WP#=1 and SRWD bit=0, or WP#=0 and SRWD bit=0, or WP#=1 and SRWD=1	The protected area cannot be program or erase.
Hardware protection mode (HPM)	The SRWD, BP0-BP3 of status register bits cannot be changed	WP#=0, SRWD bit=1	The protected area cannot be program or erase.

Note:

1. As defined by the values in the Block Protect (BP3, BP2, BP1, BP0) bits of the Status Register, as shown in Table 1.

As the above table showing, the summary of the Software Protected Mode (SPM) and Hardware Protected Mode (HPM).

Software Protected Mode (SPM):

- When SRWD bit=0, no matter WP#/ACC is low or high, the WREN instruction may set the WEL bit and can change the values of SRWD, BP3, BP2, BP1, BP0. The protected area, which is defined by BP3, BP2, BP1, BP0, is at software protected mode (SPM).
- When SRWD bit=1 and WP#/ACC is high, the WREN instruction may set the WEL bit can change the values of SRWD, BP3, BP2, BP1, BP0. The protected area, which is defined by BP3, BP2, BP1, BP0, is at software protected mode (SPM)



Note: If SRWD bit=1 but WP#/ACC is low, it is impossible to write the Status Register even if the WEL bit has previously been set. It is rejected to write the Status Register and not be executed.

Hardware Protected Mode (HPM):

- When SRWD bit=1, and then WP#/ACC is low (or WP#/ACC is low before SRWD bit=1), it enters the hardware protected mode (HPM). The data of the protected area is protected by software protected mode by BP3, BP2, BP1, BP0 and hardware protected mode by the WP#/ACC to against data modification.

Note: to exit the hardware protected mode requires WP#/ACC driving high once the hardware protected mode is entered. If the WP#/ACC pin is permanently connected to high, the hardware protected mode can never be entered; only can use software protected mode via BP3, BP2, BP1, BP0.

(6) Read Data Bytes (READ)

The read instruction is for reading data out. The address is latched on rising edge of SCLK, and data shifts out on the falling edge of SCLK at a maximum frequency fR. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single READ instruction. The address counter rolls over to 0 when the highest address has been reached.

The sequence of issuing READ instruction is: CS# goes low-> sending READ instruction code-> 3-byte address on SI -> data out on SO-> to end READ operation can use CS# to high at any time during data out. (see Figure. 17)

(7) Read Data Bytes at Higher Speed (FAST_READ)

The FAST_READ instruction is for quickly reading data out. The address is latched on rising edge of SCLK, and data of each bit shifts out on the falling edge of SCLK at a maximum frequency fC. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single FAST_READ instruction. The address counter rolls over to 0 when the highest address has been reached.

The sequence of issuing FAST_READ instruction is: CS# goes low-> sending FAST_READ instruction code-> 3-byte address on SI-> 1-dummy byte address on SI->data out on SO-> to end FAST_READ operation can use CS# to high at any time during data out. (see Figure. 18)

While Program/Erase/Write Status Register cycle is in progress, FAST_READ instruction is rejected without any impact on the Program/Erase/Write Status Register current cycle.

(8) 2 x I/O Read Mode (2READ)

The 2READ instruction enable double throughput of Serial Flash in read mode. The address is latched on rising edge of SCLK, and data of every two bits(interleave on 2 I/O pins) shift out on the falling edge of SCLK at a maximum frequency fT. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single 2READ instruction. The address counter rolls over to 0 when the highest address has been reached. Once writing 2READ instruction, the following address/dummy/ data out will perform as 2-bit instead of previous 1-bit.

The sequence of issuing 2READ instruction is: CS# goes low \rightarrow sending 2READ instruction \rightarrow 24-bit address interleave on SIO1 & SIO0 \rightarrow 8-bit dummy interleave on SIO1 & SIO0 \rightarrow data out interleave on SIO1 & SIO0 \rightarrow to end 2READ operation can use CS# to high at any time during data out (see Figure of 2 x I/O Read Mode Timing Waveform)



While Program/Erase/Write Status Register cycle is in progress, 2READ instruction is rejected without any impact on the Program/Erase/Write Status Register current cycle.

The 2 I/O only perform read operation. Program/Erase /Read ID/Read status/Read ID....operation do not support 2 I/O throughputs.

(9) Sector Erase (SE)

The Sector Erase (SE) instruction is for erasing the data of the chosen sector to be "1". The instruction is used for any 4K-byte sector. A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Sector Erase (SE). Any address of the sector (see table 3) is a valid address for Sector Erase (SE) instruction. The CS# must go high exactly at the byte boundary (the latest eighth of address byte been latched-in); otherwise, the instruction will be rejected and not executed.

Address bits [Am-A12] (Am is the most significant address) select the sector address.

The sequence of issuing SE instruction is: CS# goes low -> sending SE instruction code-> 3-byte address on SI -> CS# goes high. (see Figure 22)

The self-timed Sector Erase Cycle time (tSE) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be check out during the Sector Erase cycle is in progress. The WIP sets 1 during the tSE timing, and sets 0 when Sector Erase Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the page is protected by BP3, BP2, BP1, BP0 bits, the Sector Erase (SE) instruction will not be executed on the page.

(10) Block Erase (BE)

The Block Erase (BE) instruction is for erasing the data of the chosen block to be "1". The instruction is used for 64K-byte sector erase operation. A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Block Erase (BE). Any address of the block (see table 3) is a valid address for Block Erase (BE) instruction. The CS# must go high exactly at the byte boundary (the latest eighth of address byte been latched-in); otherwise, the instruction will be rejected and not executed.

The sequence of issuing BE instruction is: CS# goes low -> sending BE instruction code-> 3-byte address on SI -> CS# goes high. (see Figure 23)

The self-timed Block Erase Cycle time (tBE) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be check out during the Sector Erase cycle is in progress. The WIP sets 1 during the tBE timing, and sets 0 when Sector Erase Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the page is protected by BP3, BP2, BP1, BP0 bits, the Block Erase (BE) instruction will not be executed on the page.

(11) Chip Erase (CE)

The Chip Erase (CE) instruction is for erasing the data of the whole chip to be "1". A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Chip Erase (CE). Any address of the sector (see table 3) is a valid address for Chip Erase (CE) instruction. The CS# must go high exactly at the byte boundary (the latest eighth of address byte been latched-in); otherwise, the instruction will be rejected and not executed.

The sequence of issuing CE instruction is: CS# goes low-> sending CE instruction code-> CS# goes high. (see Figure 24)



The self-timed Chip Erase Cycle time (tCE) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be check out during the Chip Erase cycle is in progress. The WIP sets 1 during the tCE timing, and sets 0 when Chip Erase Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the chip is protected by BP3, BP2, BP1, BP0 bits, the Chip Erase (CE) instruction will not be executed. It will be only executed when BP3, BP2, BP1, BP0 all set to "0".

(12) Page Program (PP)

The Page Program (PP) instruction is for programming the memory to be "0". A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Page Program (PP). If the eight least significant address bits (A7-A0) are not all 0, all transmitted data which goes beyond the end of the current page are programmed from the start address if the same page (from the address whose 8 least significant address bits (A7-A0) are all 0). The CS# must keep during the whole Page Program cycle. The CS# must go high exactly at the byte boundary(the latest eighth of address byte been latched-in); otherwise, the instruction will be rejected and not executed. If more than 256 bytes are sent to the device, the data of the last 256-byte is programmed at the request page and previous data will be disregarded. If less than 256 bytes are sent to the device, the data is programmed at the request address of the page without effect on other address of the same page.

The sequence of issuing PP instruction is: CS# goes low-> sending PP instruction code-> 3-byte address on SI-> at least 1-byte on data on SI-> CS# goes high. (see Figure 20)

The self-timed Page Program Cycle time (tPP) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be check out during the Page Program cycle is in progress. The WIP sets 1 during the tPP timing, and sets 0 when Page Program Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the page is protected by BP3, BP2, BP1, BP0 bits, the Page Program (PP) instruction will not be executed.

(13) Continuously program mode (CP mode)

The CP mode may enhance program performance by automatically increasing address to the next higher address after each byte data has been programmed.

The Continuously program (CP) instruction is for multiple byte program to Flash. A write Enable (WREN) instruction must execute to set the Write Enable Latch(WEL) bit before sending the Continuously program (CP) instruction. CS# requires to go high before CP instruction is executing. After CP instruction and address input, two bytes of data is input sequentially from MSB(bit7) to LSB(bit0). The first byte data will be programmed to the initial address range with A0=0 and second byte data with A0=1. If only one byte data is input, the CP mode will not process. If more than two bytes data are input, the additional data will be ignored and only two byte data are valid. The CP program instruction will be ignored and not affect the WEL bit if it is applied to a protected memory area. Any byte to be programmed should be in the erase state (FF) first. It will not roll over during the CP mode, once the last unprotected address has been reached, the chip will exit CP mode and reset write Enable Latch bit (WEL) as "0" and CP mode bit as "0". Please check the WIP bit status if it is not in write progress before entering next valid instruction. During CP mode, the valid commands are CP command (AD hex), WRDI command (04 hex), RDSR command (05 hex), RDPR command (A1 hex), and RDSCUR command (2B hex). And the WRDI command is valid after completion of a CP programming cycle, which means the WIP bit=0.

The sequence of issuing CP instruction is: CS# high to low-> sending CP instruction code-> 3-byte address on SI-> Data Byte on SI-> CS# goes high to low-> sending CP instruction.....-> last desired byte programmed or sending Write Disable (WRDI) instruction to end CP mode-> sending RDSR instruction to verify if CP mode is ended. (see Figure of CP mode timing waveform)

Three methods to detect the completion of a program cycle during CP mode:

1) Software method-I: by checking WIP bit of Status Register to detect the completion of CP mode.



- 2) Software method-II: by waiting for a tBP time out to determine if it may load next valid command or not.
- 3) Hardware method: by writing ESRY (enable SO to output RY/BY#) instruction to detect the completion of a program cycle during CP mode. The ESRY instruction must be executed before CP mode execution. Once it is enable in CP mode, the CS# goes low will drive out the RY/BY# status on SO, "0" indicates busy stage, "1" indicates ready stage, SO pin outputs tri-state if CS# goes high. DSRY (disable SO to output RY/BY#) instruction to disable the SO to output RY/BY# and return to status register data output during CP mode. Please note that the ESRY/DSRY command are not accepted unless the completion of CP mode.

(14) Deep Power-down (DP)

The Deep Power-down (DP) instruction is for setting the device on the minimizing the power consumption (to entering the Deep Power-down mode), the standby current is reduced from ISB1 to ISB2). The Deep Power-down mode requires the Deep Power-down (DP) instruction to enter, during the Deep Power-down mode, the device is not active and all Write/Program/Erase instruction are ignored. When CS# goes high, it's only in standby mode not deep power-down mode. It's different from Standby mode.

The sequence of issuing DP instruction is: CS# goes low-> sending DP instruction code-> CS# goes high. (see Figure 25)

Once the DP instruction is set, all instruction will be ignored except the Release from Deep Power-down mode (RDP) and Read Electronic Signature (RES) instruction. (those instructions allow the ID being reading out). When Power-down, the deep power-down mode automatically stops, and when power-up, the device automatically is in standby mode. For RDP instruction the CS# must go high exactly at the byte boundary (the latest eighth bit of instruction code been latched-in); otherwise, the instruction will not executed. As soon as Chip Select (CS#) goes high, a delay of tDP is required before entering the Deep Power-down mode and reducing the current to ISB2.

(15) Release from Deep Power-down (RDP), Read Electronic Signature (RES)

The Release from Deep Power-down (RDP) instruction is terminated by driving Chip Select (CS#) High. When Chip Select (CS#) is driven High, the device is put in the Stand-by Power mode. If the device was not previously in the Deep Power-down mode, the transition to the Stand-by Power mode is immediate. If the device was previously in the Deep Power-down mode, though, the transition to the Stand-by Power mode is delayed by tRES2, and Chip Select (CS#) must remain High for at least tRES2(max), as specified in Table 6. Once in the Stand-by Power mode, the device waits to be selected, so that it can receive, decode and execute instructions.

RES instruction is for reading out the old style of 8-bit Electronic Signature, whose values are shown as table of ID Definitions. This is not the same as RDID instruction. It is not recommended to use for new design. For new design, please use RDID instruction. Even in Deep power-down mode, the RDP and RES are also allowed to be executed, only except the device is in progress of program/erase/write cycle; there's no effect on the current program/erase/write cycle in progress.

The sequence is shown as Figure 26,27.

The RES instruction is ended by CS# goes high after the ID been read out at least once. The ID outputs repeatedly if continuously send the additional clock cycles on SCLK while CS# is at low. If the device was not previously in Deep Powerdown mode, the device transition to standby mode is immediate. If the device was previously in Deep Power-down mode, there's a delay of tRES2 to transit to standby mode, and CS# must remain to high at least tRES2(max). Once in the standby mode, the device waits to be selected, so it can be receive, decode, and execute instruction.

The RDP instruction is for releasing from Deep Power Down Mode.

(16) Read Electronic Manufacturer ID & Device ID (REMS), (REMS2)

The REMS & REMS2 instruction is an alternative to the Release from Power-down/Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID.

The REMS & REMS2 instruction is very similar to the Release from Power-down/Device ID instruction. The instruction is initiated by driving the CS# pin low and shift the instruction code "90h" or "EFh" followed by two dummy bytes and one bytes address (A7~A0). After which, the Manufacturer ID for MXIC (C2h) and the Device ID are shifted out on the falling edge of SCLK with most significant bit (MSB) first as shown in figure 25. The Device ID values are listed in Table of ID Definitions. If the one-byte address is initially set to 01h, then the device ID will be read first and then followed by the Manufacturer ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

Table 7. ID Definitions

Command Type	MX25L1605D				MX25L3205D			MX25L6405D			
DDID (IEDEC ID)	Manufacturer ID	Memory type	Memory Density	Manufacturer ID	Memory type	Memory Density	Manufacturer ID	Memory type	Memory Density		
RDID (JEDEC ID)	C2	20	15	C2	20	16	C2	20	17		
RES	Electronic ID		Electronic ID			Electronic ID					
KEO	14			15		16					
REMS/REMS2	Manufacturer ID	Device ID		Manufacturer ID	Device ID		Manufacturer ID	Device ID			
KEIVIO/KEIVIOZ	C2	14		C2	15		C2	16			

(17) Enter Secured OTP (ENSO)

The ENSO instruction is for entering the additional 512-bit secured OTP mode. The additional 512-bit secured OTP is independent from main array, which may use to store unique serial number for system identifier. After entering the Secured OTP mode, and then follow standard read or program, procedure to read out the data or update data. The Secured OTP data cannot be updated again once it is lock-down.

The sequence of issuing ENSO instruction is: CS# goes low-> sending ENSO instruction to enter Secured OTP mode -> CS# goes high.

Please note that WRSR/WRSCUR commands are not acceptable during the access of secure OTP region, once security OTP is lock down, only read related commands are valid.

(18) Exit Secured OTP (EXSO)

The EXSO instruction is for exiting the additional 512-bit secured OTP mode.

The sequence of issuing EXSO instruction is: CS# goes low-> sending EXSO instruction to exit Secured OTP mode-> CS# goes high.

(19) Read Security Register (RDSCUR)

The RDSCUR instruction is for reading the value of Security Register bits. The Read Security Register can be read at any time (even in program/erase/write status register/write security register condition) and continuously.

The sequence of issuing RDSCUR instruction is: CS# goes low-> sending RDSCUR instruction -> Security Register data out on SO-> CS# goes high.

The definition of the Security Register bits is as below:

Secured OTP Indicator bit. The Secured OTP indicator bit shows the chip is locked by factory before ex-factory or not. When it is "0", it indicates non-factory lock; "1" indicates factory-lock.

Lock-down Secured OTP (LDSO) bit. By writing WRSCUR instruction, the LDSO bit may be set to "1" for customer lock-down purpose. However, once the bit is set to "1" (lock-down), the LDSO bit and the 512-bit Secured OTP area cannot be update any more. While it is in 512-bit secured OTP mode, array access is not allowed.

Table 8. Security Register Definition

bit7	bit6	bit5	bit4	bit3	bit2	bit1	bit0
х	х	х	х	х	х	LDSO (indicate if lock-down	Secrured OTP indicator bit
reserved	reserved	reserved	reserved	reserved	reserved	0 = not lock- down 1 = lock-down (cannot program/erase OTP)	factory lock
volatile bit	non-volatile bit	non-volatile bit					

(20) Write Security Register (WRSCUR)

The WRSCUR instruction is for changing the values of Security Register Bits. Unlike write status register, the WREN instruction is not required before sending WRSCUR instruction. The WRSCUR instruction may change the values of bit1 (LDSO bit) for customer to lock-down the 512-bit Secured OTP area. Once the LDSO bit is set to "1", the Secured OTP area cannot be updated any more.

The sequence of issuing WRSCUR instruction is :CS# goes low-> sending WRSCUR instruction -> CS# goes high.

The CS# must go high exactly at the boundary; otherwise, the instruction will be rejected and not executed.



POWER-ON STATE

The device is at below states when power-up:

- Standby mode (please note it is not deep power-down mode)
- Write Enable Latch (WEL) bit is reset

The device must not be selected during power-up and power-down stage unless the VCC achieves below correct level:

- VCC minimum at power-up stage and then after a delay of tVSL
- -GND at power-down

Please note that a pull-up resistor on CS# may ensure a safe and proper power-up/down level.

An internal power-on reset (POR) circuit may protect the device from data corruption and inadvertent data change during power up state. When VCC is lower than VWI (POR threshold voltage value), the internal logic is reset and the flash device has no response to any command.

For further protection on the device, after VCC reaching the VWI level, a tPUW time delay is required before the device is fully accessible for commands like write enable(WREN), page program (PP), Continuously Program (CP), sector erase(SE), chip erase(CE), WRSCUR and write status register(WRSR). If the VCC does not reach the VCC minimum level, the correct operation is not guaranteed. The write, erase, and program command should be sent after the below time delay:

- tPUW after VCC reached VWI level
- tVSL after VCC reached VCC minimum level

The device can accept read command after VCC reached VCC minimum and a time delay of tVSL, even time of tPUW has not passed.

Please refer to the figure of "power-up timing".

Note:

- To stabilize the VCC level, the VCC rail decoupled by a suitable capacitor close to package pins is recommended.(generally around 0.1uF)
- At power-down stage, the VCC drops below VWI level, all operations are disable and device has no response to any command. The data corruption might occur during the stage while a write, program, erase cycle is in progress.

ELECTRICAL SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS

RATING	VALUE	
Ambient Operating Temperature	-40° C to 85° C for Industrial grade	
Storage Temperature	-55° C to 125° C	
Applied Input Voltage	-0.5V to 4.6V	
Applied Output Voltage	-0.5V to 4.6V	
VCC to Ground Potential	-0.5V to 4.6V	

NOTICE:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is stress rating only and functional operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended period may affect reliability.
- 2. Specifications contained within the following tables are subject to change.
- 3. During voltage transitions, all pins may overshoot Vss to -2.0V and Vcc to +2.0V for periods up to 20ns, see Figure 4, 5.

Figure 4.Maximum Negative Overshoot Waveform

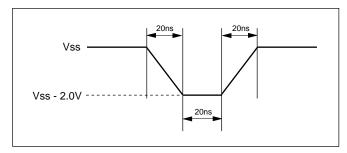
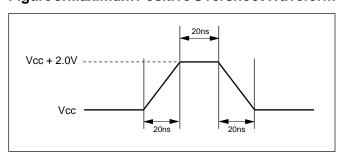


Figure 5. Maximum Positive Overshoot Waveform



CAPACITANCE TA = 25°C, f = 1.0 MHz

SYMBOL	PARAMETER	MIN.	TYP	MAX.	UNIT	CONDITIONS
CIN	Input Capacitance			6	pF	VIN = 0V
COUT	Output Capacitance			8	pF	VOUT = 0V



Figure 6. INPUT TEST WAVEFORMS AND MEASUREMENT LEVEL

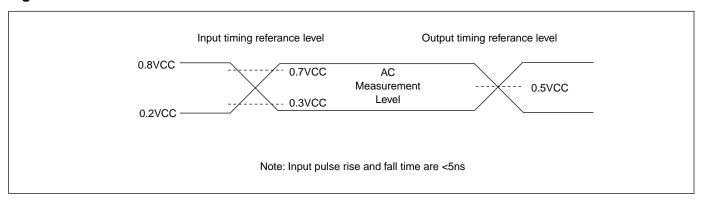


Figure 7. OUTPUT LOADING

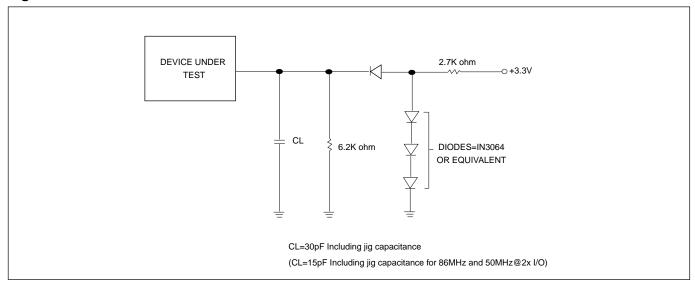




Table 9. DC CHARACTERISTICS (Temperature = -40°C to 85°C for Industrial grade, VCC = 2.7V ~ 3.6V)

•	•				•		•
SYMBOL	PARAMETER	NOTES	MIN.	TYP	MAX.	UNITS	TEST CONDITIONS
ILI	Input Load	1			± 2	uA	VCC = VCC Max
	Current						VIN = VCC or GND
ILO	Output Leakage	1			± 2	uA	VCC = VCC Max
	Current						VIN = VCC or GND
ILIHV	HV pin input Leakage				35	uA	WP#/ACC=10.5V
	Current						
ISB1	VCC Standby	1			20	uA	VIN = VCC or GND
	Current						CS# = VCC
ISB2	Deep Power-down				20	uA	VIN = VCC or GND
	Current						CS# = VCC
ICC1	VCC Read	1			25	mA	f=86MHz
							fT=50MHz (2 x I/O read)
							SCLK=0.1VCC/0.9VCC, SO=Open
					20	mA	f=66MHz
							SCLK=0.1VCC/0.9VCC, SO=Open
					10	mA	f=33MHz
							SCLK=0.1VCC/0.9VCC, SO=Open
ICC2	VCC Program	1			20	mA	Program in Progress
	Current (PP)						CS# = VCC
ICC3	VCC Write Status				20	mA	Program status register in progress
	Register (WRSR)						CS#=VCC
	Current						
ICC4	VCC Sector Erase	1			20	mA	Erase in Progress
	Current (SE)						CS#=VCC
ICC5	VCC Chip Erase	1			20	mA	Erase in Progress
	Current (CE)						CS#=VCC
VHH	Voltage for ACC Progr	ram/	9.5		10.5	V	VCC=2.7V~3.6V
	Erase Acceleration						
VIL	Input Low Voltage		-0.5		0.3VCC	V	
VIH	Input High Voltage		0.7VCC		VCC+0.4	· V	
VOL	Output Low Voltage				0.4	V	IOL = 1.6mA
VOH	Output High Voltage		VCC-0.2			V	IOH = -100uA





Table 10. AC CHARACTERISTICS

(Temperature = -40° C to 85° C for Industrial grade, VCC = 2.7V ~ 3.6V)

Symbol	Alt.	Parameter			Min.	Тур.	Max.	Unit
fSCLK	fC	Clock Frequency for the following	instructions:		10KHz		86	MHz
		FAST_READ, PP, SE, BE, CE, D		(Co	ndition:1	5pF)		
		WREN, WRDI, RDID, RDSR, WRS	SR				66	MHz
						(Co	ndition:3	0pF)
fRSCLK	fR	Clock Frequency for READ instruc	ctions		10KHz		33	MHz
fTSCLK	fΤ	Clock Frequency for 2READ instru	uctions		10KHz		50	MHz
						(Co	ndition:1	5pF)
tCH(1)	tCLH	Clock High Time			7			ns
tCL(1)	tCLL	Clock Low Time			7			ns
tCLCH(2)		Clock Rise Time (3) (peak to peak	:)		0.1			V/ns
tCHCL(2)		Clock Fall Time (3) (peak to peak)			0.1			V/ns
tSLCH	tCSS	CS# Active Setup Time (relative to	SCLK)		5			ns
tCHSL		CS# Not Active Hold Time (relativ	e to SCLK)		5			ns
tDVCH	tDSU	Data In Setup Time			2			ns
tCHDX	tDH	Data In Hold Time			5			ns
tCHSH		CS# Active Hold Time (relative to	5			ns		
tSHCH		CS# Not Active Setup Time (relati	ve to SCLK)	l	5			ns
tSHSL	tCSH	CS# Deselect Time			100			ns
tSHQZ(2)	tDIS	Output Disable Time	64Mb/	2.7V-3.6V			10	ns
			32Mb/	3.0V-3.6V			8	ns
			16Mb					
tCLQV	tV	Clock Low to Output Valid	64Mb/	2.7V-3.6V			10	ns
			32Mb/	3.0V-3.6V			8	ns
			16Mb					
tCLQX	tHO	Output Hold Time			0			ns
tHLCH		HOLD# Setup Time (relative to SC	CLK)		5			ns
tCHHH		HOLD# Hold Time (relative to SCL	.K)		5			ns
tHHCH		HOLD Setup Time (relative to SCL	_K)		5			ns
tCHHL		HOLD Hold Time (relative to SCL)	()		5			ns
tHHQX(2)	tLZ	HOLD to Output Low-Z	64Mb/	2.7V-3.6V			10	ns
			32Mb/	3.0V-3.6V			8	ns
			16Mb					
tHLQZ(2)	tHZ	HOLD# to Output High-Z	64Mb/	2.7V-3.6V			10	ns
			32Mb/	3.0V-3.6V			8	ns
			16Mb					
tWHSL(4)		Write Protect Setup Time	<u> </u>		20			ns
tSHWL(4)		Write Protect Hold Time			100			ns
tDP(2)		CS# High to Deep Power-down Mo	ode				10	us
tRES1(2)		CS# High to Standby Mode withou	ıt Electronic	Signature Rea	d		8.8	us
tRES2(2)		CS# High to Standby Mode with E	lectronic Sia	nature Read			8.8	us



Symbol	Alt.	Parameter		Min.	Тур.	Max.	Unit
tW		Write Status Register Cycle Time			40	100	ms
tBP		Byte-Program			9	300	us
tPP		Page Program Cycle Time			1.4	5	ms
tSE		Sector Erase Cycle Time			60	300	ms
tBE		Block Erase Cycle Time			0.7	2	S
tCE		Chip Erase Cycle Time	64Mb		50	80	S
			32Mb		25	50	S
			16Mb		14	30	s

Notes

- 1. tCH + tCL must be greater than or equal to 1/ fC. For Fast Read, tCL/tCH=5.5/5.5.
- 2. Value guaranteed by characterization, not 100% tested in production.
- 3. Expressed as a slew-rate.
- 4. Only applicable as a constraint for a WRSR instruction when SRWD is set at 1.
- 5. Test condition is shown as Figure 6.

Table 11. Power-Up Timing and VWI Threshold

Symbol	Parameter	Min.	Max.	Unit
tVSL(1)	VCC(min) to CS# low	200		us
tPUW(1)	Time delay to Write instruction	1	10	ms
VWI(1)	Write Inhibit Voltage	1.5	2.5	V

Note: 1. These parameters are characterized only.

INITIAL DELIVERY STATE

The device is delivered with the memory array erased: all bits are set to 1 (each byte contains FFh). The Status Register contains 00h (all Status Register bits are 0).



Figure 8. Serial Input Timing

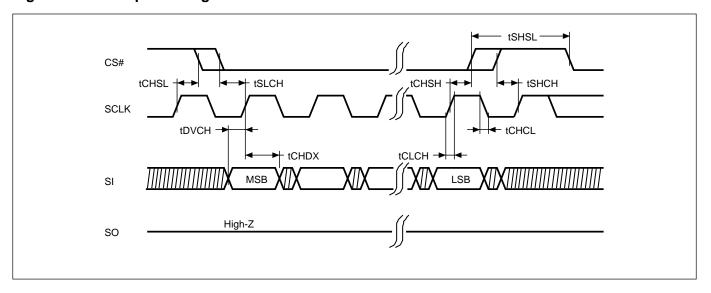


Figure 9. Output Timing

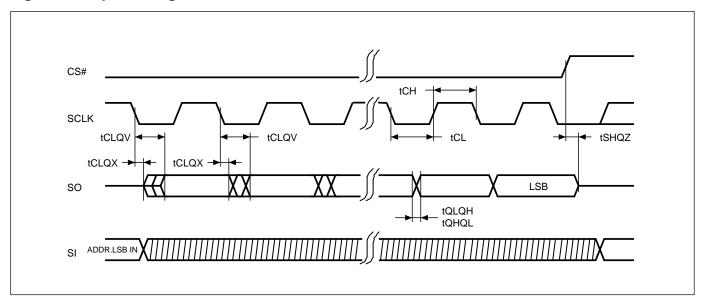
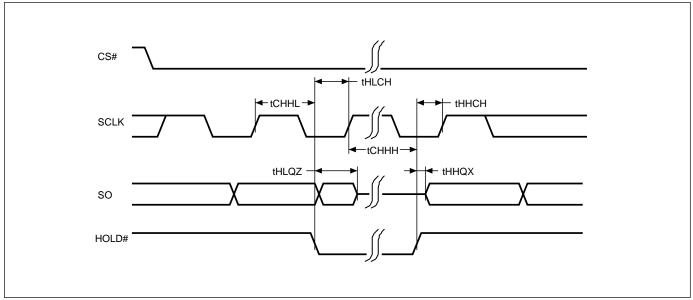




Figure 10. Hold Timing



^{*} SI is "don't care" during HOLD operation.

Figure 11. WP# Disable Setup and Hold Timing during WRSR when SRWD=1

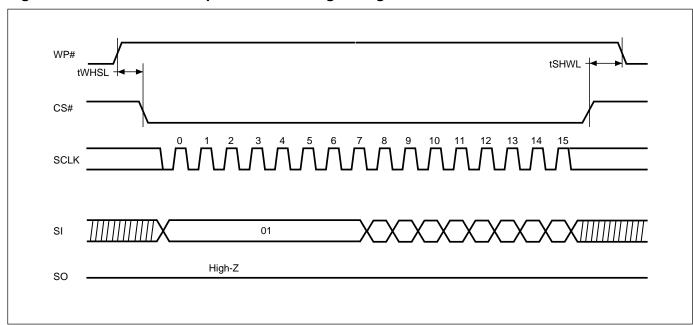




Figure 12. Write Enable (WREN) Sequence (Command 06)

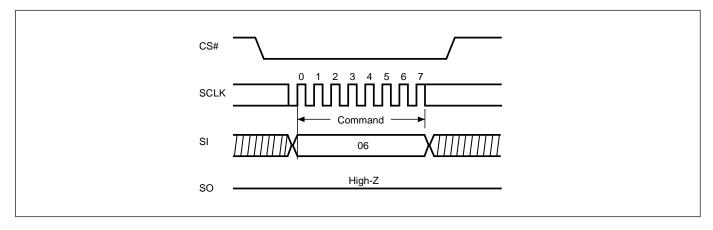


Figure 13. Write Disable (WRDI) Sequence (Command 04)

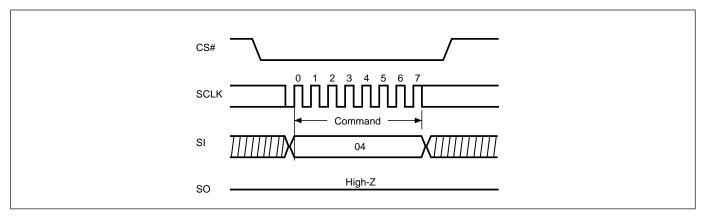


Figure 14. Read Identification (RDID) Sequence (Command 9F)

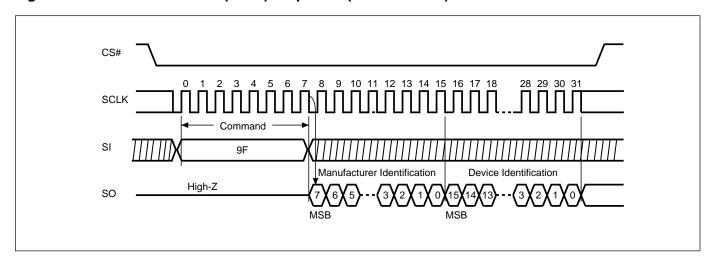




Figure 15. Read Status Register (RDSR) Sequence (Command 05)

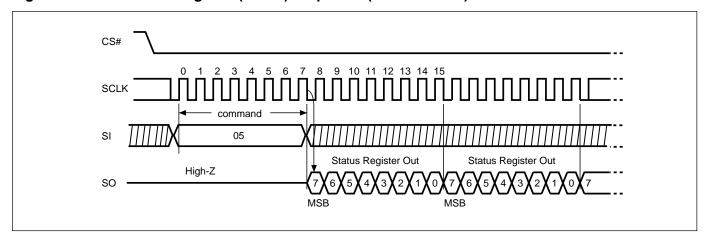


Figure 16. Write Status Register (WRSR) Sequence (Command 01)

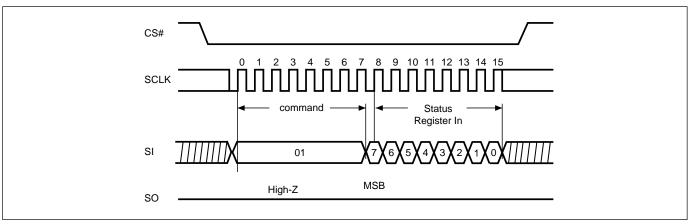


Figure 17. Read Data Bytes (READ) Sequence (Command 03)

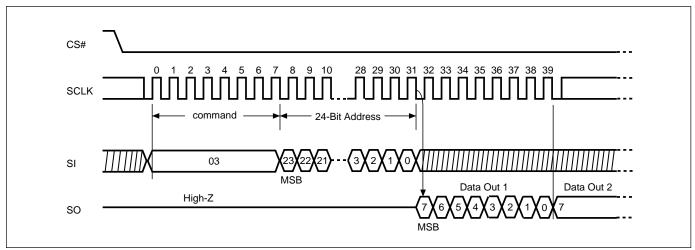




Figure 18. Read at Higher Speed (FAST_READ) Sequence (Command 0B)

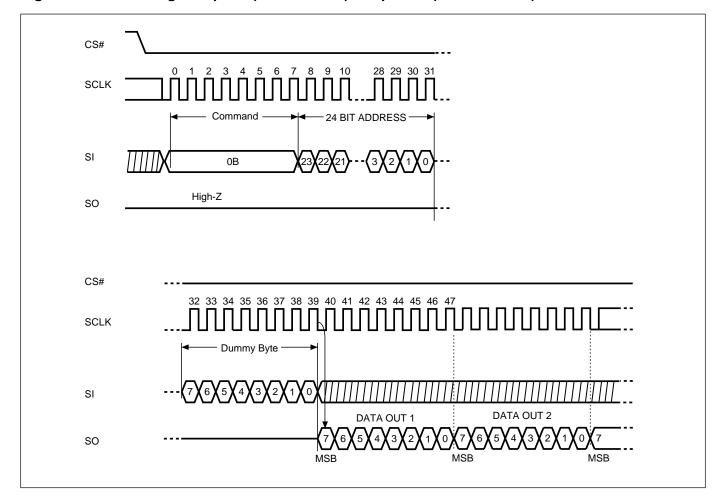




Figure 19. 2 x I/O Read Mode Sequence (Command BB)

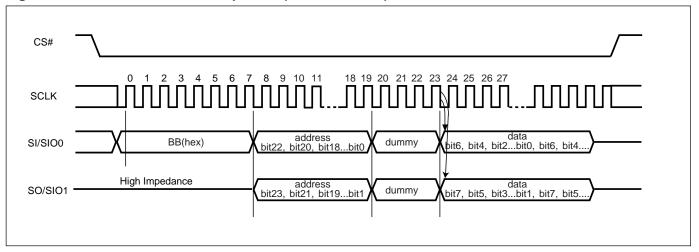


Figure 20. Page Program (PP) Sequence (Command 02)

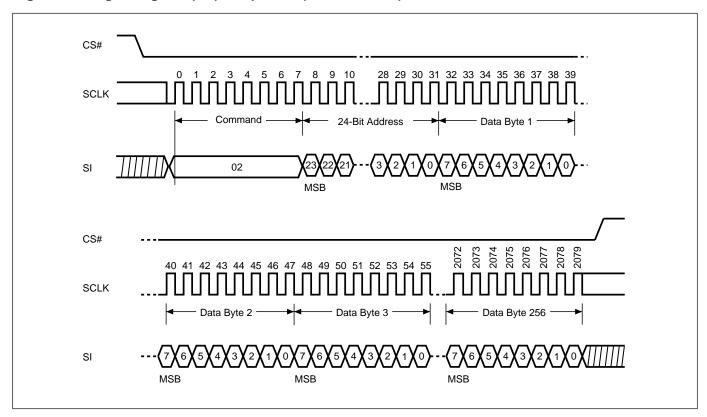
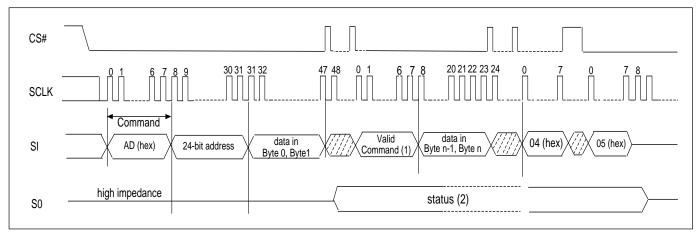




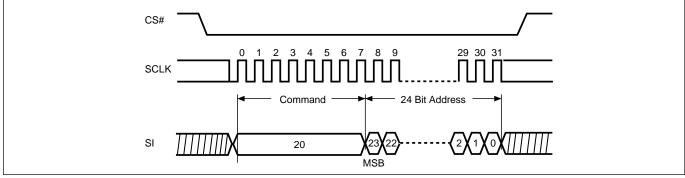
Figure 21. Continously Program (CP) Mode Sequence with Hardware Detection (Command AD)



Note: (1) During CP mode, the valid commands are CP command (AD hex), WRDI command (04 hex), RDSR command (05 hex), RDPR command (A1 hex), and RDSCUR command (2B hex).

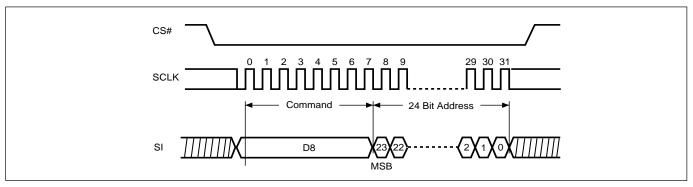
- (2) Once an internal programming operation begins, CS# goes low will drive the status on the SO pin and CS# goes high will return the SO pin to tri-state.
- (3) To end the CP mode, either reaching the highest unprotected address or sending Write Disable (WRDI) command (04 hex) may achieve it and then it is recommended to send RDSR command (05 hex) to verify if CP mode is ended

Figure 22. Sector Erase (SE) Sequence (Command 20)



Note: SE command is 20(hex).

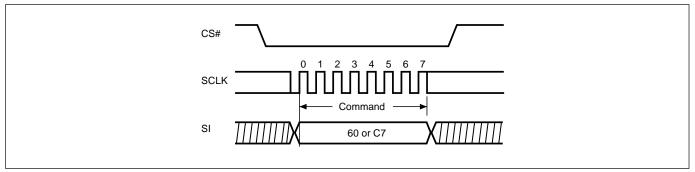
Figure 23. Block Erase (BE) Sequence (Command D8)



Note: BE command is D8(hex).



Figure 24. Chip Erase (CE) Sequence (Command 60 or C7)



Note: CE command is 60(hex) or C7(hex).

Figure 25. Deep Power-down (DP) Sequence (Command B9)

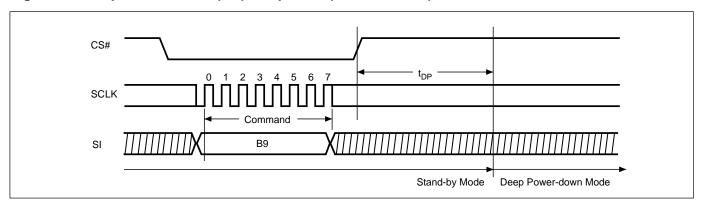


Figure 26. Release from Deep Power-down and Read Electronic Signature (RES) Sequence (Command AB)

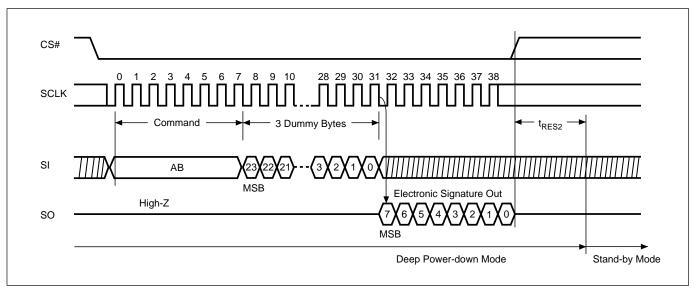




Figure 27. Release from Deep Power-down (RDP) Sequence (Command AB)

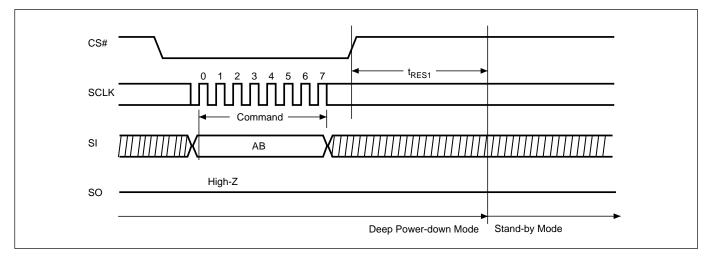
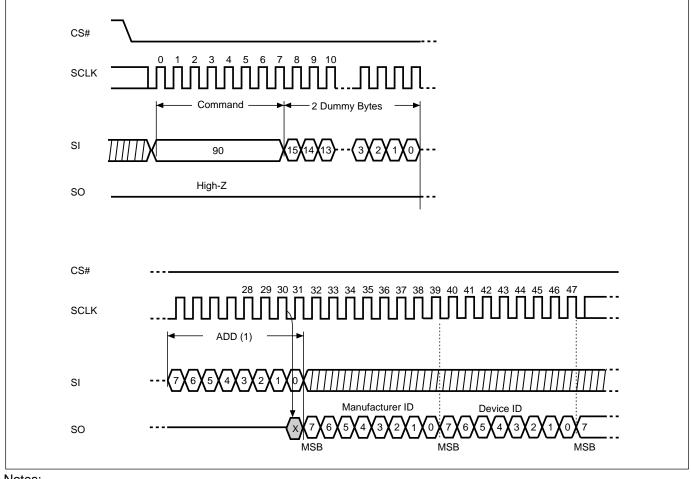


Figure 28. Read Electronic Manufacturer & Device ID (REMS) Sequence (Command 90 or EF)

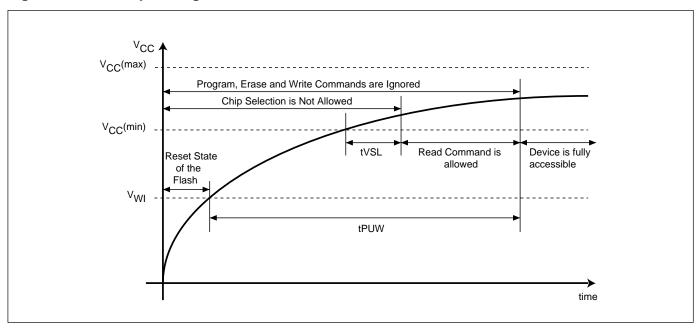


Notes:

(1) ADD=00H will output the manufacturer's ID first and ADD=01H will output device ID first

(2) Instruction is either 90(hex) or EF(hex).

Figure 29. Power-up Timing



Note: VCC (max.) is 3.6V and VCC (min.) is 2.7V.

RECOMMENDED OPERATING CONDITIONS

At Device Power-Up

AC timing illustrated in Figure A is recommended for the supply voltages and the control signals at device power-up. If the timing in the figure is ignored, the device may not operate correctly.

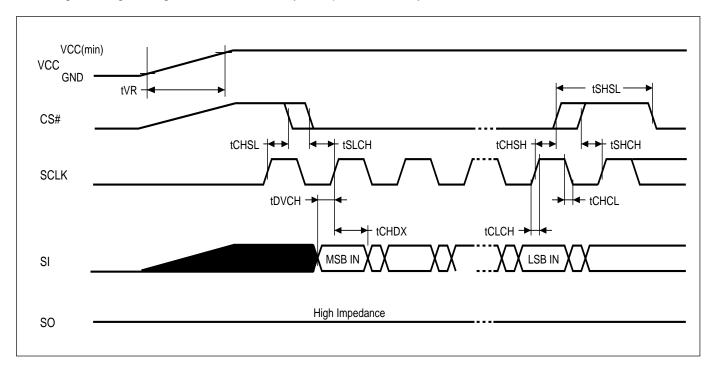


Figure A. AC Timing at Device Power-Up

Symbol	Parameter	Notes	Min.	Max.	Unit
tVR	VCC Rise Time	1	20	500000	us/V

Notes:

- 1. Sampled, not 100% tested.
- 2. For AC spec tCHSL, tSLCH, tDVCH, tCHDX, tSHSL, tCHSH, tSHCH, tCHCL, tCLCH in the figure, please refer to "AC CHARACTERISTICS" table.

ERASE AND PROGRAMMING PERFORMANCE

PARAMETER		Min.	TYP. (1)	Max. (2)	UNIT
Write Status Register Cycle Time			40	100	ms
Sector Erase Time			60	300	ms
Block Erase Time			0.7	2	s
	64Mb		50	80	S
Chip Erase Time	32Mb		25	50	S
	16Mb		14	30	S
	64Mb		30	48	S
Chip Erase Time (at ACC mode)	32Mb		15	30	s
	16Mb		8	18	S
Byte Program Time (via page program con	Byte Program Time (via page program command)				us
Page Program Time		1.4	5	ms	
Page Program Time (at ACC mode)		1.4	5	ms	
Erase/Program Cycle		100,000		cycles	

Note:

- 1. Typical program and erase time assumes the following conditions: 25° C, 3.3V, and checker board pattern.
- 2. Under worst conditions of 85° C and 2.7V.
- 3. System-level overhead is the time required to execute the first-bus-cycle sequence for the programming command.
- 4. Erase/Program cycles comply with JEDEC JESD-47E & A117A standard.

LATCH-UP CHARACTERISTICS

	MIN.	MAX.
Input Voltage with respect to GND on ACC	-1.0V	10.5V
Input Voltage with respect to GND on all power pins, SI, CS#	-1.0V	2 VCCmax
Input Voltage with respect to GND on SO	-1.0V	VCC + 1.0V
Current	-100mA	+100mA
Includes all pins except VCC. Test conditions: VCC = 3.0V, one pin at a time.	•	

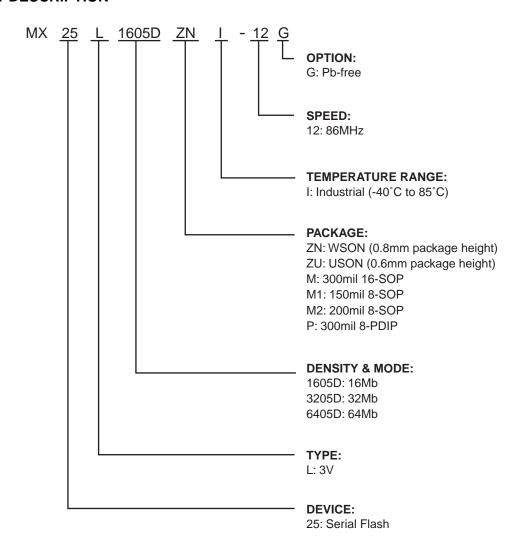


MX25L1605D MX25L3205D MX25L6405D

ORDERING INFORMATION

PARTNO.	CLOCK (MHz)	OPERATING CURRENT MAX.	STANDBY CURRENT MAX	Temperature (.	PACKAGE	Remark
		(mA)	(uA)			
MX25L1605DM2I-12G	86	25	20	-40° C~85° C	8-SOP (200mil)	Pb-free
MX25L1605DMI-12G	86	25	20	-40° C~85° C	16-SOP	Pb-free
MX25L1605DM1I-12G	86	25	20	-40° C~85° C	8-SOP (150mil)	Pb-free
MX25L1605DPI-12G	86	25	20	-40° C~85° C	8-PDIP (300mil)	Pb-free
MX25L1605DZNI-12G	86	25	20	-40° C~85° C	8-WSON (6x5mm)	Pb-free
MX25L1605DZUI-12G	86	25	20	-40° C~85° C	8-USON (4x4mm)	Pb-free
MX25L3205DZNI-12G	86	25	20	-40° C~85° C	8-WSON (6x5mm)	Pb-free
MX25L3205DM2I-12G	86	25	20	-40° C~85° C	8-SOP (200mil)	Pb-free
MX25L3205DMI-12G	86	25	20	-40° C~85° C	16-SOP	Pb-free
MX25L3205DPI-12G	86	25	20	-40° C~85° C	8-PDIP (300mil)	Pb-free
MX25L3205DZUI-12G	86	25	20	-40° C~85° C	8-USON (4x4mm)	Pb-free
MX25L6405DZNI-12G	86	25	20	-40° C~85° C	8-WSON (8x6mm)	Pb-free
MX25L6405DMI-12G	86	25	20	-40° C~85° C	16-SOP	Pb-free

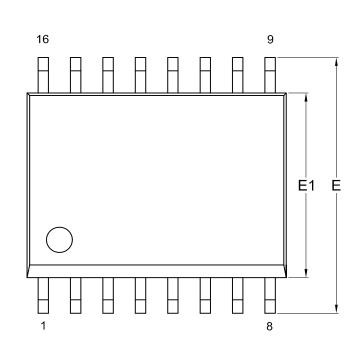
PART NAME DESCRIPTION

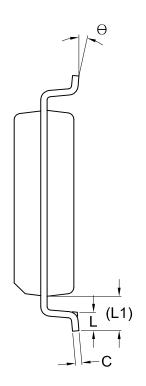


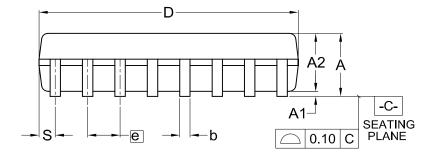


PACKAGE INFORMATION

Title: Package Outline for SOP 16L (300MIL)





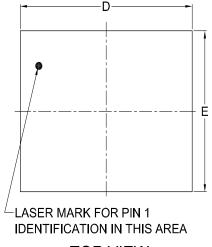


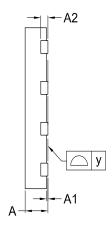
SY	MBOL	Α	A 1	A2	b	С	D	E	E1	е	L	L1	s	θ
	Min.		0.10	2.25	0.36	0.20	10.10	10.10	7.42		0.40	1.31	0.51	0
mm	Nom.	-	0.20	2.31	0.41	0.25	10.30	10.30	7.52	1.27	0.84	1.44	0.64	5
	Max.	2.65	0.30	2.40	0.51	0.30	10.50	10.50	7.60	-	1.27	1.57	0.77	8
	Min.	-	0.004	0.089	0.014	0.008	0.397	0.397	0.292		0.016	0.052	0.020	0
Inch	Nom.		0.008	0.091	0.016	0.010	0.405	0.405	0.296	0.050	0.033	0.057	0.025	5
	Max.	0.104	0.012	0.094	0.020	0.012	0.413	0.413	0.299	-	0.050	0.062	0.030	8

DWC NO	REVISION		REFERENCE	ICCLIE DATE	
DWG.NO.	REVISION	JEDEC	ISSUE DATE		
6110-1402	8	MS-013			03-07-'06

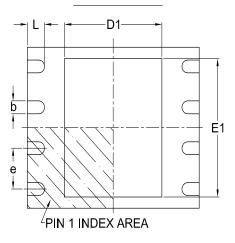


Title: Package Outline for WSON 8L (6x5x0.8MM, LEAD PITCH 1.27MM)





TOP VIEW



SIDE VIEW

BOTTOM VIEW

Dimensions (inch dimensions are derived from the original mm dimensions)

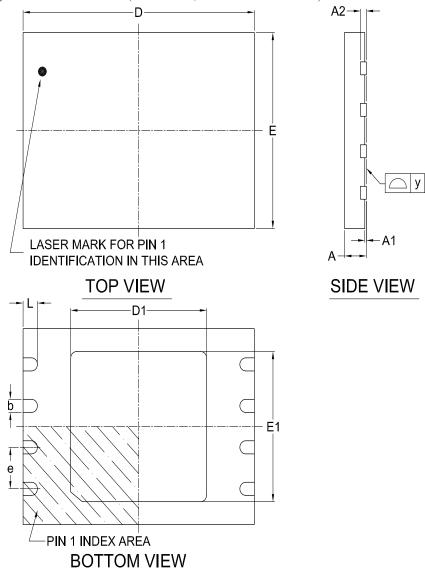
*1 : This package has exposed metal pad underneath the package, it can't contact to metal trace or pad on board.

*2 : The exposed pad size must not violate the min. metal separtion requirement, 0.2mm with terminals.

UNIT	MBOL	Α	A 1	A2	b	D	D1	E	E1	L	е	у
	Min.	0.70	-	-	0.35	5.90	3.30	4.90	3.90	0.50		0.00
mm	Nom.	_		0.20	0.40	6.00	3.40	5.00	4.00	0.60	1.27	_
	Max.	0.80	0.05	1	0.48	6.10	3.50	5.10	4.10	0.75	1	0.08
	Min.	0.028		-	0.014	0.232	0.129	0.193	0.154	0.020	1	0.00
Inch	Nom.	_		0.008	0.016	0.236	0.134	0.197	0.157	0.024	0.05	_
	Max.	0.032	0.002	ļ	0.019	0.240	0.138	0.201	0.161	0.030	_	0.003

DWC NO	REVISION		ICCUE DATE		
DWG.NO.	REVISION	JEDEC	ISSUE DATE		
6110-3401	4	MO-220			2007/09/20

Doc. Title: Package Outline for WSON 8L (8x6x0.8MM, LEAD PITCH 1.27MM)



Dimensions (inch dimensions are derived from the original mm dimensions)

*1 : This package has exposed metal pad underneath the package, it can't contact to metal trace or pad on board.

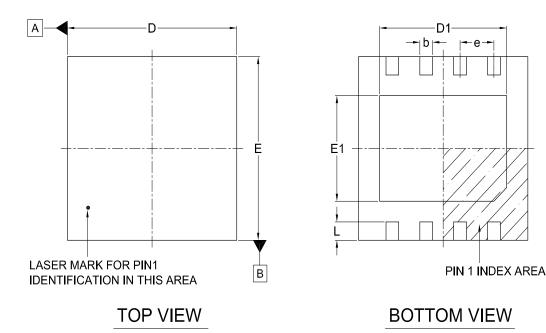
*2 : The exposed pad size must not violate the min. metal separtion requirement, 0.2mm with terminals.

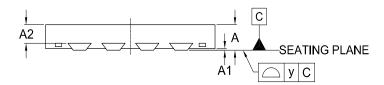
UNIT	MBOL	Α	A1	A2	b	D	D1	E	E1	L	е	у
	Min.	0.70			0.35	7.90	4.65	5.90	4.55	0.40	1	0.00
mm	Nom.	-		0.20	0.40	8.00	4.70	6.00	4.60	0.50	1.27	_
	Max.	0.80	0.05	1	0.48	8.10	4.75	6.10	4.65	0.60	1	0.08
	Min.	0.028		_	0.014	0.311	0.183	0.232	0.179	0.016	_	0.00
Inch	Nom.			0.008	0.016	0.315	0.185	0.236	0.181	0.020	0.05	
	Max.	0.032	0.002		0.019	0.319	0.187	0.240	0.183	0.024	_	0.003

Dave No	Revision	Reference						
Dwg. No.	Revision	JEDEC	EIAJ					
6110-3402	5	MO-220						



Title: Package Outline for USON 8L (4x4x0.6MM, LEAD PITCH 0.8MM)





SIDE VIEW

Dimensions (inch dimensions are derived from the original mm dimensions)

*1 : This package has exposed metal pad underneath the package, it can't contact to metal trace or pad on board.

*2 : The exposed pad size must not violate the min. metal separtion requirement, 0.2mm with terminals.

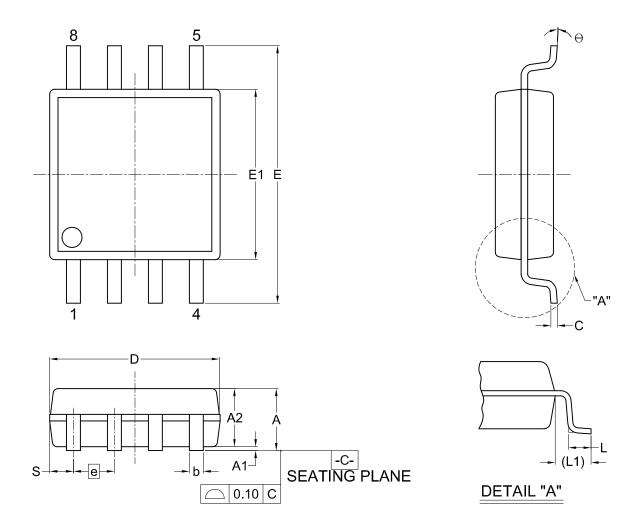
UNIT	MBOL	Α	A1	A2	b	D	D1	E	E1	L	е	у
	Min.	0.50	-	1	0.25	3.90	2.90	3.90	2.20	0.35	1	0.00
mm	Nom.	0.55	0.04	0.40	0.30	4.00	3.00	4.00	2.30	0.40	0.80	
	Max.	0.60	0.05	0.43	0.35	4.10	3.10	4.10	2.40	0.45	-	0.08
	Min.	0.020		_	0.010	0.154	0.114	0.154	0.087	0.014	-	0.00
Inch	Nom.	0.022	0.002	0.016	0.011	0.157	0.118	0.157	0.091	0.016	0.031	_
	Max.	0.024	0.002	0.017	0.014	0.161	0.122	0.161	0.094	0.018	I	0.003

DWG.NO.	DEVISION	REVISION REFERENCE					
DWG.NO.	REVISION	JEDEC	ISSUE DATE				
6110-3601	3	MO - 252			2008/03/12		

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Title: Package Outline for SOP 8L 200MIL (official name - 209MIL)

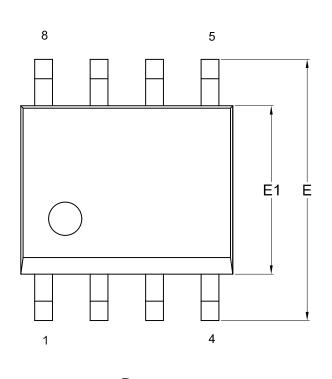


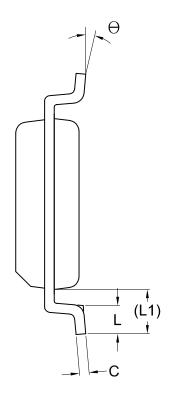
UNIT	MBOL	Α	A 1	A2	b	С	D	E	E1	е	L	L1	s	θ
	Min.		0.05	1.70	0.36	0.19	5.13	7.70	5.18		0.50	1,21	0.62	0
	-									4.07				5
	Nom.		0.15	1.80	0.41	0.20	5.23	7.90	5.28	1.27	0.65	1.31	0.74	
	Max.	2.16	0.25	1.91	0.51	0.25	5.33	8.10	5.38		0.80	1.41	0.88	8
	Min.		0.002	0.067	0.014	0.007	0.202	0.303	0.204		0.020	0.048	0.024	0
	Nom.	1	0.006	0.071	0.016	0.008	0.206	0.311	0.208	0.050	0.026	0.052	0.029	5
	Max.	0.009	0.010	0.075	0.020	0.010	0.210	0.319	0.212		0.031	0.056	0.035	8

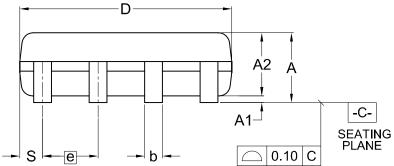
DWG.NO.	REVISION		ISSUE DATE		
DWG.NO.	REVISION	JEDEC	EIAJ		1990E DATE
6110-1406	1				05-06-'05



Title: Package Outline for SOP 8L (150MIL)





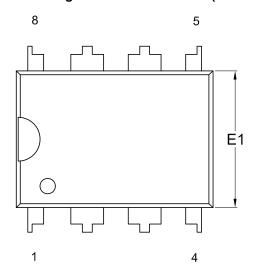


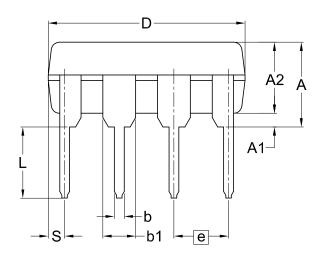
SY UNIT	MBOL	Α	A 1	A2	b	С	D	E	E1	е	L	L1	s	θ
	MIn.		0.10	1.35	0.36	0.15	4.77	5.80	3.80		0.46	0.85	0.41	0
mm	Nom.	-	0.15	1.45	0.41	0.20	4.90	5.99	3.90	1.27	0.66	1.05	0.54	5
	Max.	1.75	0.20	1.55	0.51	0.25	5.03	6.20	4.00		0.86	1.25	0.67	8
	Min.		0.004	0.053	0.014	0.006	0.188	0.228	0.150		0.018	0.033	0.016	0
Inch	Nom.		0.006	0.057	0.016	0.008	0.193	0.236	0.154	0.050	0.026	0.041	0.021	5
	Max.	0.069	0.008	0.061	0.020	0.010	0.198	0.244	0.158		0.034	0.049	0.026	8

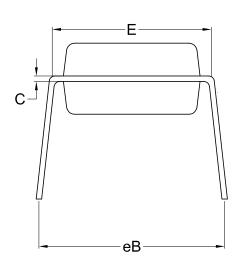
DWC NO	DEVISION		ICCUE DATE			
DWG.NO.	REVISION	JEDEC	EIAJ		ISSUE DATE	
6110-1401	6	MS-012			11-26-'03	



Title: Package Outline for PDIP 8L (300MIL)







SY	MBOL	A	A 1	A2	b	b1	С	D	E	E1	е	eВ	L	s
	Min.	I	0.38	3.18	0.36	1.14	0.20	9.02	7.62	6.22	1	7.87	2.92	0.76
mm	Nom.	1		3.30	0.46	1.52	0.25	9.27	7.87	6.35	2.54	8.89	3.30	1.14
	Max.	5.33		3.43	0.56	1.78	0.36	10.16	8.13	6.48	1	9.53	3.81	1.52
	Min.		0.015	0.125	0.014	0.045	0.008	0.355	0.300	0.245	1	0.310	0.115	0.030
Inch	Nom.	1		0.130	0.018	0.060	0.010	0.365	0.310	0.250	0.100	0.350	0.130	0.045
	Max.	0.210		0.135	0.022	0.070	0.014	0.400	0.320	0.255	_	0.375	0.150	0.060

DWC NO	REVISION		ISSUE DATE			
DWG.NO.	REVISION	JEDEC	EIAJ		ISSUE DATE	
6110-0201	6	MS-001			09-01-'06	



MX25L1605D MX25L3205D MX25L6405D

REVISION HISTORY

Revision No.	Description	Page	Date
1.0	1. Removed "Preliminary"	P1	MAR/07/2008
1.1	1. Dual I/O Pre-released	P1,3,21,31	MAY/12/2008
1.2	1. Added 8-land USON package information	P2,4,46,47,5	50 JUL/08/2008
1.3	1. Modified figure 4 & 5 waveform	P28	AUG/15/2008
	2. Revised VHH spec from 11.0V(typ.)~11.5V(max.) to	P4,8,30,45	
	9.5V(min.)~10.5V(max.)		
1.4	1. Revised sector erase time spec from 90ms(typ.) to 60ms(typ.)	P32,45	OCT/01/2008
	2. Removed "Advanced Information" for MX25L3205DZUI-12G	P46	

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